

# Fixed-frequency 800 V / 950 V CoolSET™

## in DIP-7 package

### Features

- Integrated 800 V / 950 V avalanche rugged CoolMOS™
- Enhanced Active Burst mode with selectable entry and exit standby power
- Digital frequency reduction for better overall system efficiency
- Fast startup achieved with cascode configuration
- DCM and CCM operation with slope compensation
- Frequency jitter and soft gate driving for low EMI
- Built-in digital soft start
- Integrated error amplifier to support direct feedback in non-isolated flyback and buck topologies
- Comprehensive protection with input line overvoltage,  $V_{CC}$  overvoltage,  $V_{CC}$  undervoltage, overload, open loop and overtemperature
- All protections are in auto restart mode
- Limited charging current for  $V_{CC}$  short to GND
- Pb-free lead plating, halogen-free mold compound, RoHS-compliant



PG-DIP-7

### Potential applications

- Auxiliary power supply for home appliances, white goods, TV, PC and server, smart metering
- Blu-ray players, set-top boxes, and LCD/LED monitors

### Product validation

Fully qualified according to JEDEC for Industrial Applications.

### Description

The ICE5xRxxxxxZ is the fifth-generation of fixed-frequency integrated power IC (CoolSET™) optimized for off-line switch-mode power supplies in cascode configuration. The CoolSET™ package contains two separate chips. One is the controller chip and the other is the 800 V / 950 V CoolMOS™ chip. The cascode configuration helps achieve fast startup. The frequency reduction with soft gate driving and frequency jitter operation offers lower EMI and better efficiency between a light load and 50% load. The selectable entry and exit standby power ABM enables flexibility and ultra-low power consumption in standby mode with small and controllable output voltage ripple. The product has a wide operating range (10.0 V to 25.5 V) of IC power supply and lower power consumption. The numerous protection functions support the power supply system in failure situations. All these make the fifth-generation CoolSET™ series an outstanding integrated power stage fixed frequency flyback and buck converter in the market.

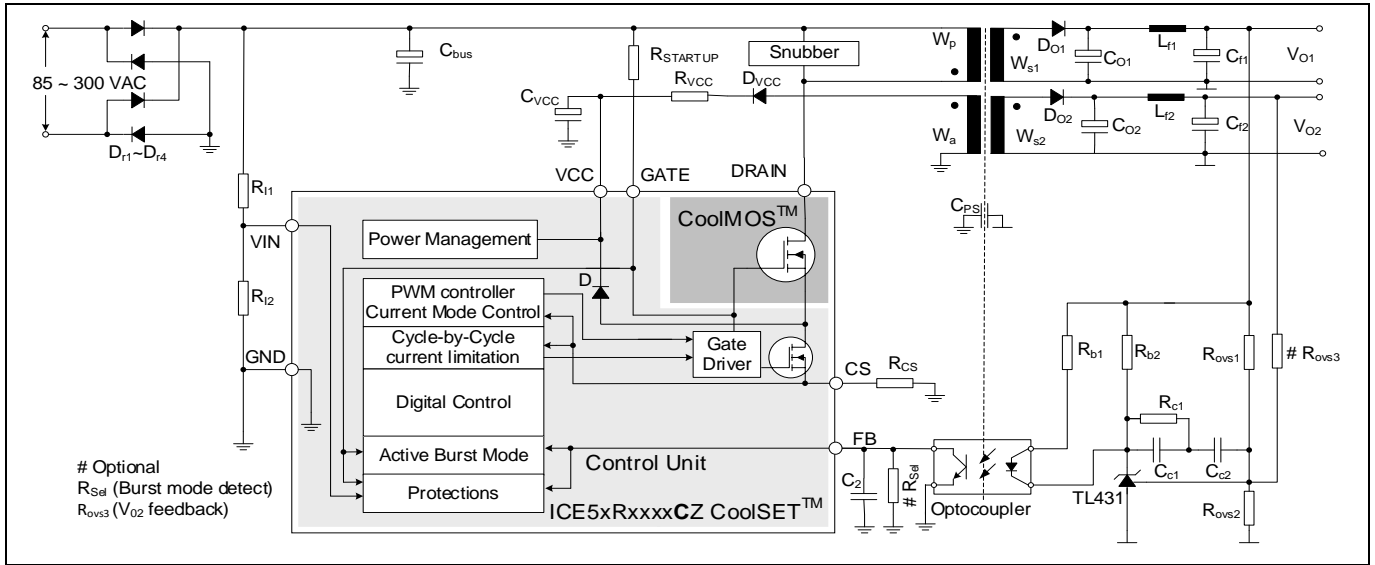


Figure 1 Typical application in isolated flyback using TL431 and optocoupler

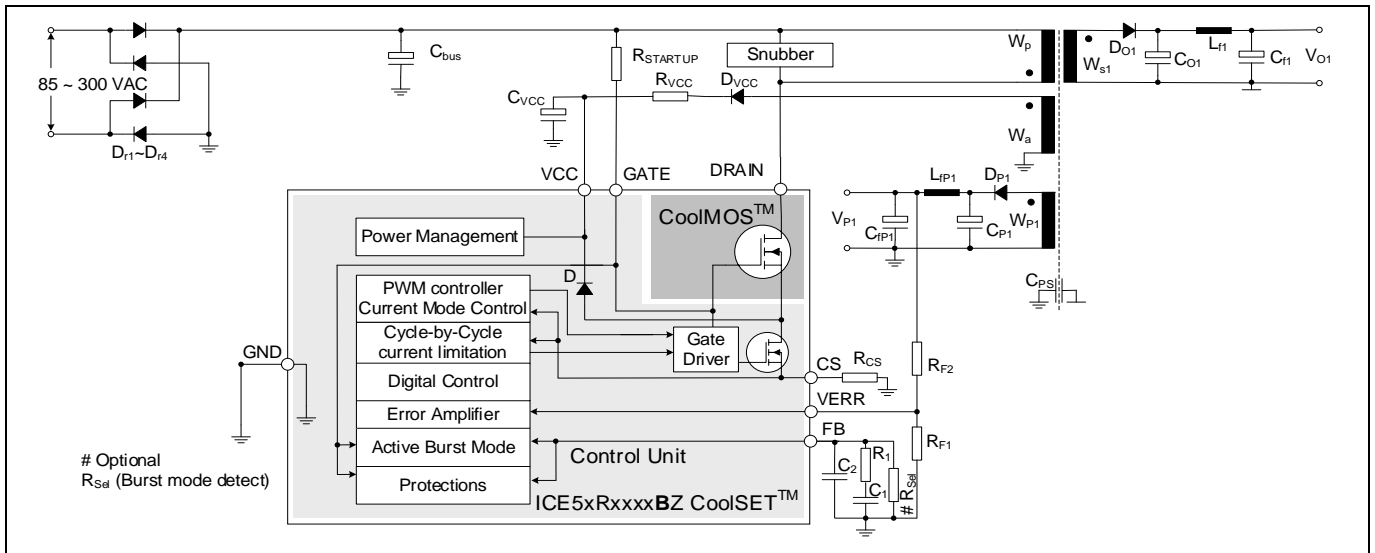


Figure 2 Typical application in non-isolated flyback utilizing integrated error amplifier

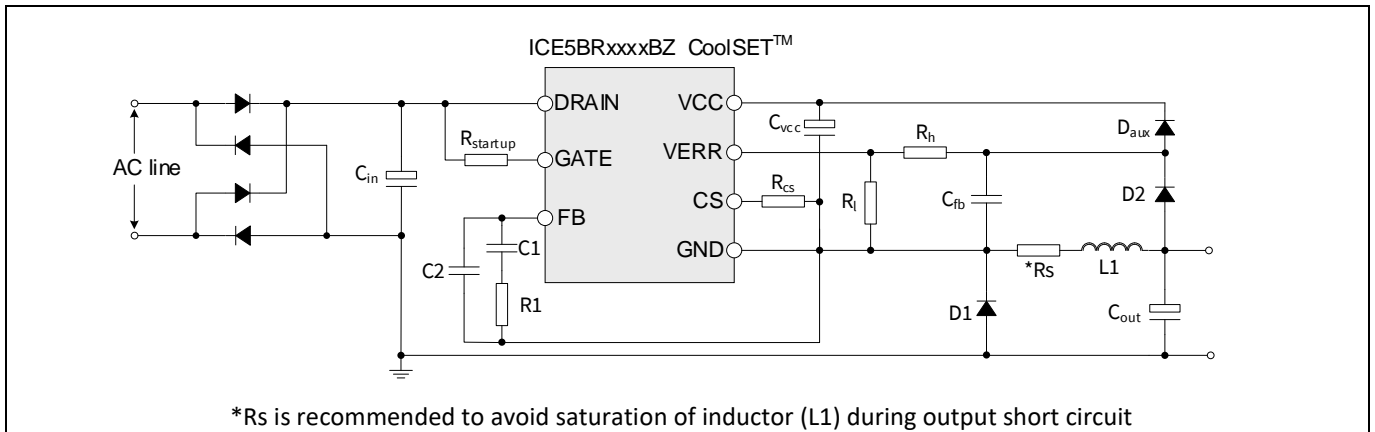


Figure 3 Typical application in non-isolated buck

**Output power of fifth-generation fixed-frequency CoolSET™ in flyback design**

**Table 1 Output power of fifth-generation fixed-frequency CoolSET™ in flyback design**

Type	Package	Marking	V <sub>DS</sub>	F <sub>sw</sub>	R <sub>Dson</sub> <sup>1</sup>	220 V AC ±20% <sup>2</sup> at DCM	85-300 V AC <sup>2</sup> at DCM	85-300 V AC <sup>2</sup> at CCM
ICE5BR4780BZ	PG-DIP-7	5BR4780BZ	800 V	65 kHz	4.13 Ω	27.5 W	15 W	16.5 W
ICE5BR3995BZ	PG-DIP-7	5BR3995BZ	950 V	65 kHz	3.46 Ω	30 W	16.5 W	18 W
ICE5BR3995CZ	PG-DIP-7	5BR3995CZ	950 V	65 kHz	3.46 Ω	30 W	16.5 W	18 W
ICE5AR3995BZ	PG-DIP-7	5AR3995BZ	950 V	100 kHz	3.46 Ω	30 W	16.5 W	18 W
ICE5BR2280BZ	PG-DIP-7	5BR2280BZ	800 V	65 kHz	2.13 Ω	40 W	22 W	24 W
ICE5AR2280CZ	PG-DIP-7	5AR2280CZ	800 V	100 kHz	2.13 Ω	40 W	22 W	24 W

**Output current of fifth-generation fixed-frequency CoolSET™ in non-isolated buck design**

Infineon® recommends the 65 kHz variant for a non-isolated Buck converter.

**Table 2 Output current of fifth-generation generation fixed-frequency CoolSET™ in non-isolated buck design**

Type	Package	Marking	V <sub>DS</sub>	F <sub>sw</sub>	R <sub>Dson</sub> <sup>1</sup>	85-265 V AC <sup>3</sup> at DCM	Typical output voltage
ICE5BR4780BZ	PG-DIP-7	5BR4780BZ	800 V	65 kHz	4.13 Ω	450 mA	15 V
ICE5BR3995BZ	PG-DIP-7	5BR3995BZ	950 V	65 kHz	3.46 Ω	550 mA	
ICE5BR2280BZ	PG-DIP-7	5BR2280BZ	800 V	65 kHz	2.13 Ω	700 mA	

<sup>1</sup> Typically at T<sub>i</sub> = 25°C (inclusive of low side MOSFET).

<sup>2</sup> Calculated maximum output power rating in an open frame design at T<sub>a</sub> = 50°C, T<sub>j</sub> = 125°C (integrated high voltage MOSFET) and using minimum drain pin copper area in a 2 oz copper single-sided PCB. The output power figure is for selection purpose only. The actual power can vary depending on the designs. Contact a technical expert from Infineon® for more information.

<sup>3</sup> Calculated maximum output current rating in an open frame design at T<sub>a</sub> = 50°C, T<sub>j</sub> = 125°C (integrated high voltage MOSFET) and using minimum 100mm<sup>2</sup> drain pin copper area in a 2 oz copper single-sided PCB. The output current figure is for selection purpose only. The actual current can vary depending on the designs. Contact a technical expert from Infineon® for more information.

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Block diagram

1 Block diagram

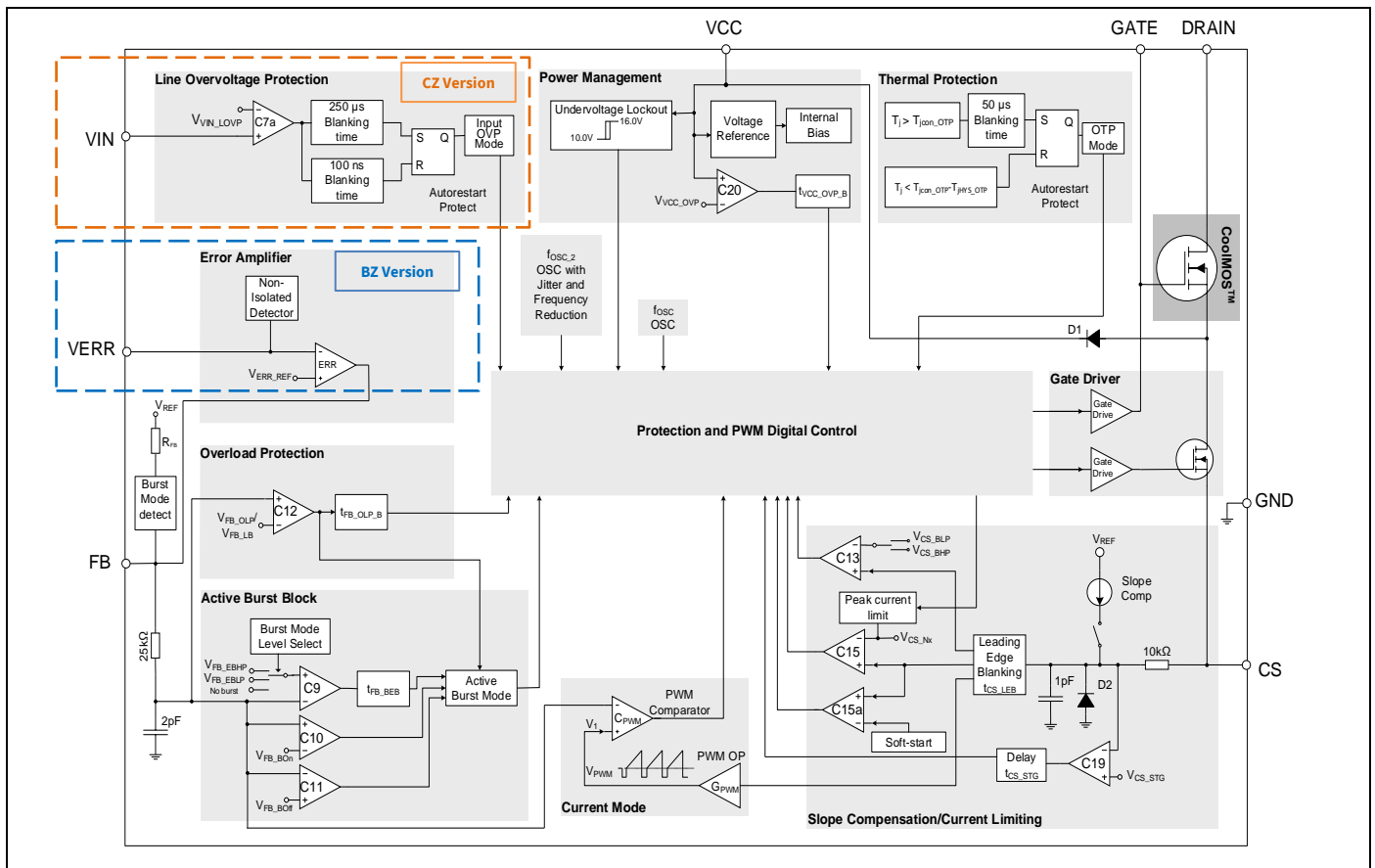
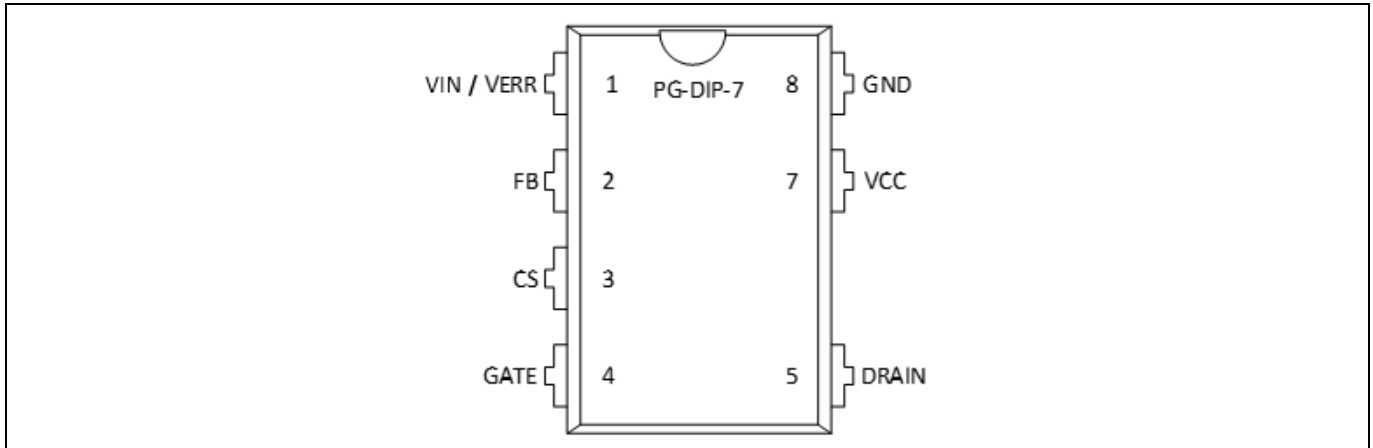


Figure 4 Block diagram

Note: Junction temperature of the controller chip is sensed for overtemperature protection. The CoolMOS™ is a separate chip from the controller chip in the same package. Refer to the design guide or consult a technical expert for the proper thermal design.

## 2 Pin configuration

The pin configuration is shown in [Figure 5](#) and the functions are described in [Table 3](#).



**Figure 5** Pin configuration

**Table 3** Pin definitions and functions

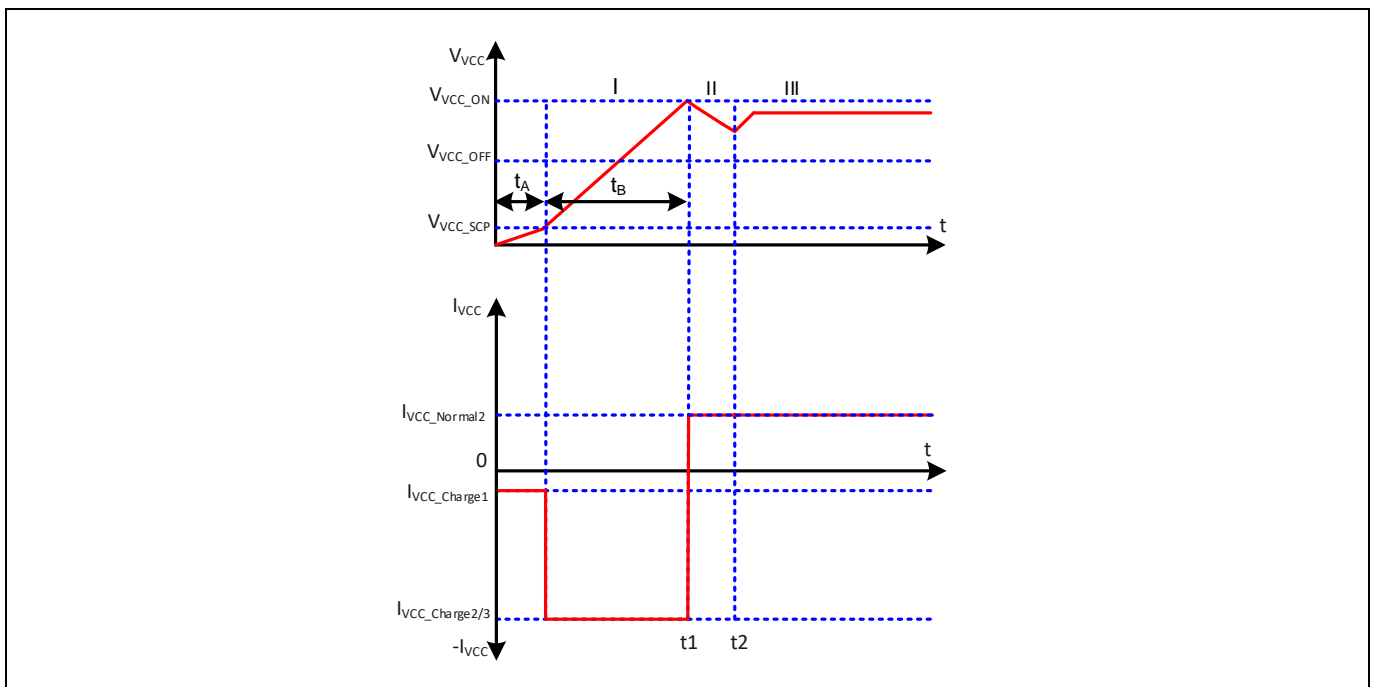
Pin	Symbol	Function
1	VERR (BZ version)	Error amplifier VERR pin is internally connected to the transconductance error amplifier for a non-isolated converter. Connect this pin to GND for an isolated converter.
	VIN (CZ version)	Input line overvoltage protection (LOVP) VIN pin is connected to the bus via a resistor divider (see <a href="#">Figure 1</a> ) to sense the line voltage. Internally, it is connected to the line overvoltage comparator which stops the switching when a LOVP condition occurs. To disable LOVP, connect this pin to GND.
2	FB	Feedback and ABM entry and exit control FB pin combines the functions of feedback control, selectable burst entry/exit control and overload/open loop protection.
3	CS	Current sense The CS pin is connected to the shunt resistor for the primary current sensing externally and to the PWM signal generator block for switch-off determination (together with the feedback voltage) internally.
4	GATE	Gate driver output The GATE pin is connected to the Gate of the internal CoolMOS™ and additionally, a pull-up resistor is connected from a bus voltage to turn on the internal CoolMOS™ for charging up the $V_{CC}$ capacitor during startup.
5	DRAIN	DRAIN (Drain of integrated CoolMOS™) The DRAIN pin is connected to the drain of the integrated CoolMOS™.
7	VCC	VCC (Positive voltage supply) The VCC pin is the positive voltage supply to the IC. The operating range is between $V_{VCC\_OFF}$ and $V_{VCC\_OVP}$ .
8	GND	Ground The GND pin is the common ground of the controller.

### 3 Functional description

#### 3.1 V<sub>CC</sub> precharging and typical V<sub>CC</sub> voltage during startup

As shown in **Figure 1**, once the line input voltage is applied, a rectified voltage appears across the capacitor C<sub>BUS</sub>. The pull-up resistor R<sub>STARTUP</sub> provides a current to charge the C<sub>ISS</sub> (input capacitance) of CoolMOS™ and gradually generate one voltage level. If the voltage over C<sub>ISS</sub> is high enough, CoolMOS™ and the V<sub>CC</sub> capacitor are charged through the primary inductance of a transformer L<sub>P</sub>, CoolMOS™ and the internal diode D<sub>1</sub> with the two steps constant current source I<sub>VCC\_Charge1</sub><sup>1</sup> and I<sub>VCC\_Charge3</sub><sup>1</sup>.

A very small constant current source (I<sub>VCC\_Charge1</sub>) is charged to the V<sub>CC</sub> capacitor until V<sub>CC</sub> reaches V<sub>VCC\_SCP</sub> to protect the controller from the V<sub>CC</sub> pin short to ground during the startup. After this, the second step constant current source (I<sub>VCC\_Charge3</sub>) is provided to charge the V<sub>CC</sub> capacitor further, until the V<sub>CC</sub> voltage exceeds the turned-on threshold V<sub>VCC\_ON</sub>. As shown in the time phase I in **Figure 6**, the V<sub>CC</sub> voltage increases almost linearly with two steps.



**Figure 6** V<sub>CC</sub> voltage and current at startup

The time for the V<sub>CC</sub> precharging can then be calculated as:

$$t_1 = t_A + t_B = \frac{V_{VCC\_SCP} \times C_{VCC}}{I_{VCC\_Charge1}} + \frac{(V_{VCC\_ON} - V_{VCC\_SCP}) \times C_{VCC}}{I_{VCC\_Charge3}} \quad (1)$$

When the V<sub>CC</sub> voltage exceeds the V<sub>CC</sub> turn on threshold V<sub>VCC\_ON</sub> at time t<sub>1</sub>, the IC starts to operate with soft start. Due to the power consumption of the IC and the fact that there is still no energy from the auxiliary winding to charge the V<sub>CC</sub> capacitor before the output voltage is built up, the V<sub>CC</sub> voltage drops (phase II). Once the output voltage rises close to regulation, the auxiliary winding starts to charge the V<sub>CC</sub> capacitor from the time t<sub>2</sub> onward and delivering the I<sub>VCC\_Normal2</sub><sup>2</sup> to the CoolSET™. V<sub>CC</sub> then reaches a constant value depending on the output load.

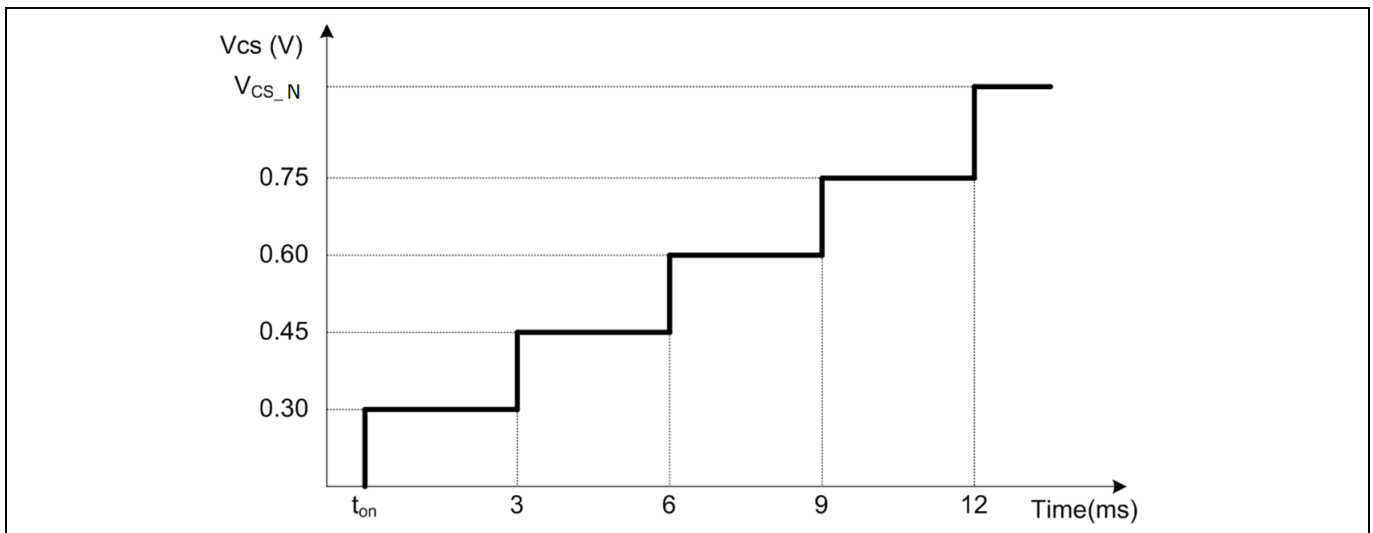
<sup>1</sup> I<sub>VCC\_Charge1/2/3</sub> is charging current from the controller to VCC capacitor during startup.

<sup>2</sup> I<sub>VCC\_Normal2</sub> is supply current from VCC capacitor or auxiliary winding to the CoolSET™ during normal operation.



## 3.2 Soft start

As shown in [Figure 7](#), the IC starts to operate with a soft start at time  $t_{on}$ . The switching stresses on the power MOSFET, diode, and transformer are minimized during soft start. The soft start implemented in ICE5xRxxxxxZ is a digital time-based function. The preset soft start time is  $t_{ss}$  (12 ms) with four steps. If not limited by other functions, the peak voltage on CS pin increases step by step from 0.3 V to finally  $V_{CS\_N}$  (0.8 V). The normal feedback loop takes over the control when the output voltage reaches its regulated value.



**Figure 7** Maximum current sense voltage during soft start

## 3.3 Normal operation

The PWM controller during normal operation consists of a digital signal processing circuit including regulation control and an analog circuit including a current measurement unit and a comparator. Details about the full operation of the CoolSET™ in normal operation are illustrated in the following paragraphs.

### 3.3.1 PWM operation and peak current mode control

#### 3.3.1.1 Switch-on determination

The power MOSFET turn-on is synchronized with the internal oscillator with a switching frequency  $F_{sw}$  that corresponds to the voltage level  $V_{FB}$  (see [Figure 9](#)).

#### 3.3.1.2 Switch-off determination

In peak current mode control, the PWM comparator monitors voltage  $V_1$  (see [Figure 4](#)), which represents the instantaneous current of the power MOSFET. When  $V_1$  exceeds  $V_{FB}$ , the PWM comparator sends a signal to switch off the GATE of the power MOSFET. Therefore, the peak current of the power MOSFET is controlled by the feedback voltage  $V_{FB}$  (see [Figure 8](#)).

At switch-on transient of the power MOSFET, a voltage spike across  $R_{CS}$  can cause  $V_1$  to increase and exceed  $V_{FB}$ . To avoid a false switch off, the IC has a blanking time  $t_{CS\_LEB}$  before detecting the voltage across  $R_{CS}$  to mask the voltage spike. Therefore, the minimum turn on time of the power MOSFET is  $t_{CS\_LEB}$ .

If the voltage level at  $V_1$  takes a long time to exceed  $V_{FB}$ , the IC has implemented a maximum duty cycle control to force the power MOSFET to switch off when  $D_{MAX} = 0.75$  is reached.

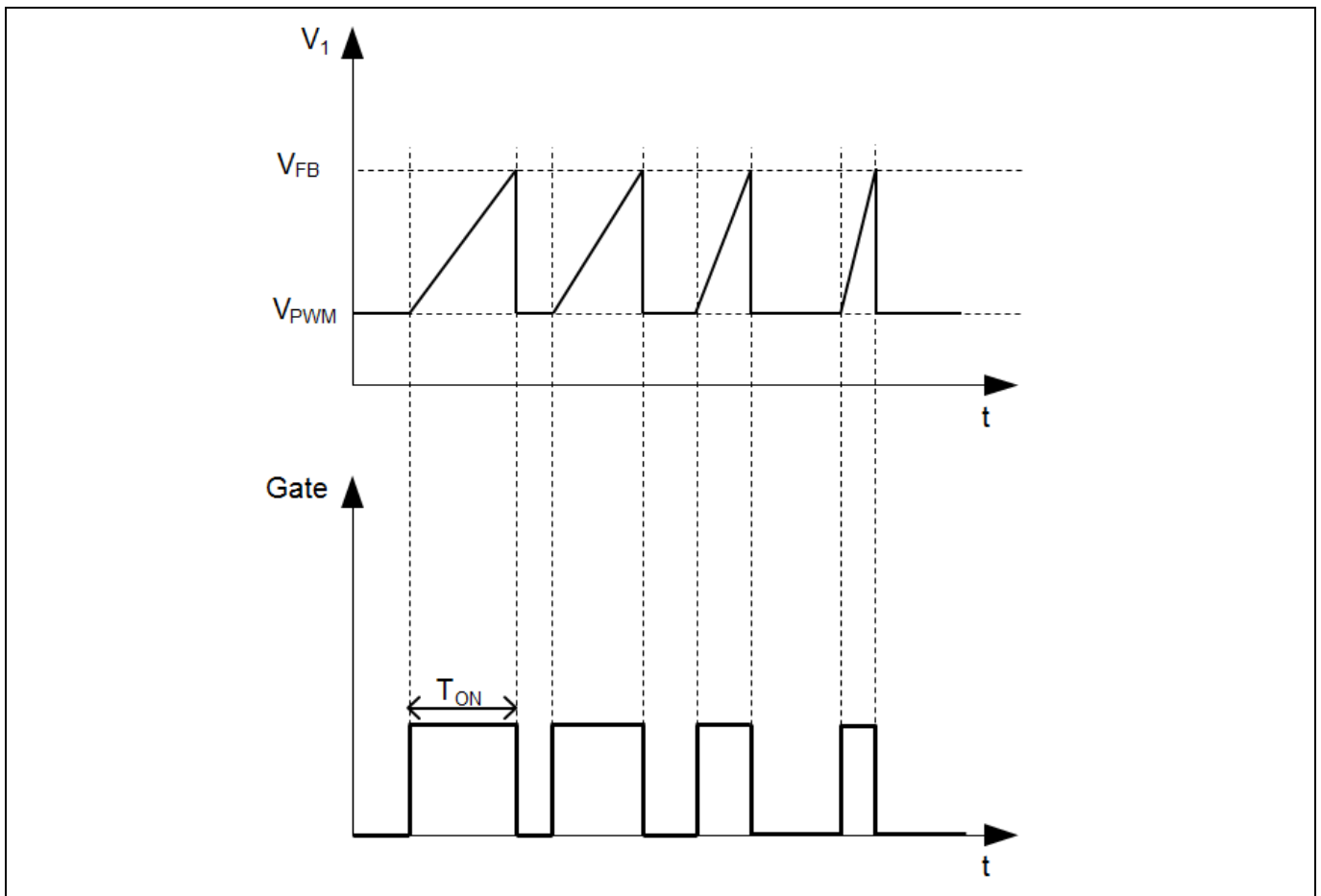


Figure 8 Pulse width modulation

### 3.3.2 Current sense

The power MOSFET current generates a voltage  $V_{CS}$  across the current sense resistor  $R_{CS}$  connected between the CS pin and the GND pin.  $V_{CS}$  is amplified with gain  $G_{PWM}$ , then, added with an offset  $V_{PWM}$  to become  $V_1$  as described below in equation 3.

$$V_{CS} = I_D \times R_{CS} \tag{2}$$

$$V_1 = V_{CS} \times G_{PWM} + V_{PWM} \tag{3}$$

where:

- $V_{CS}$  : CS pin voltage
- $I_D$  : Power MOSFET current
- $R_{CS}$  : Resistance of the current sense resistor
- $V_1$  : Voltage level compared to  $V_{FB}$  as described in chapter [3.3.1.2](#)
- $G_{PWM}$  : PWM-OP gain
- $V_{PWM}$  : Offset for voltage ramp

### Functional description

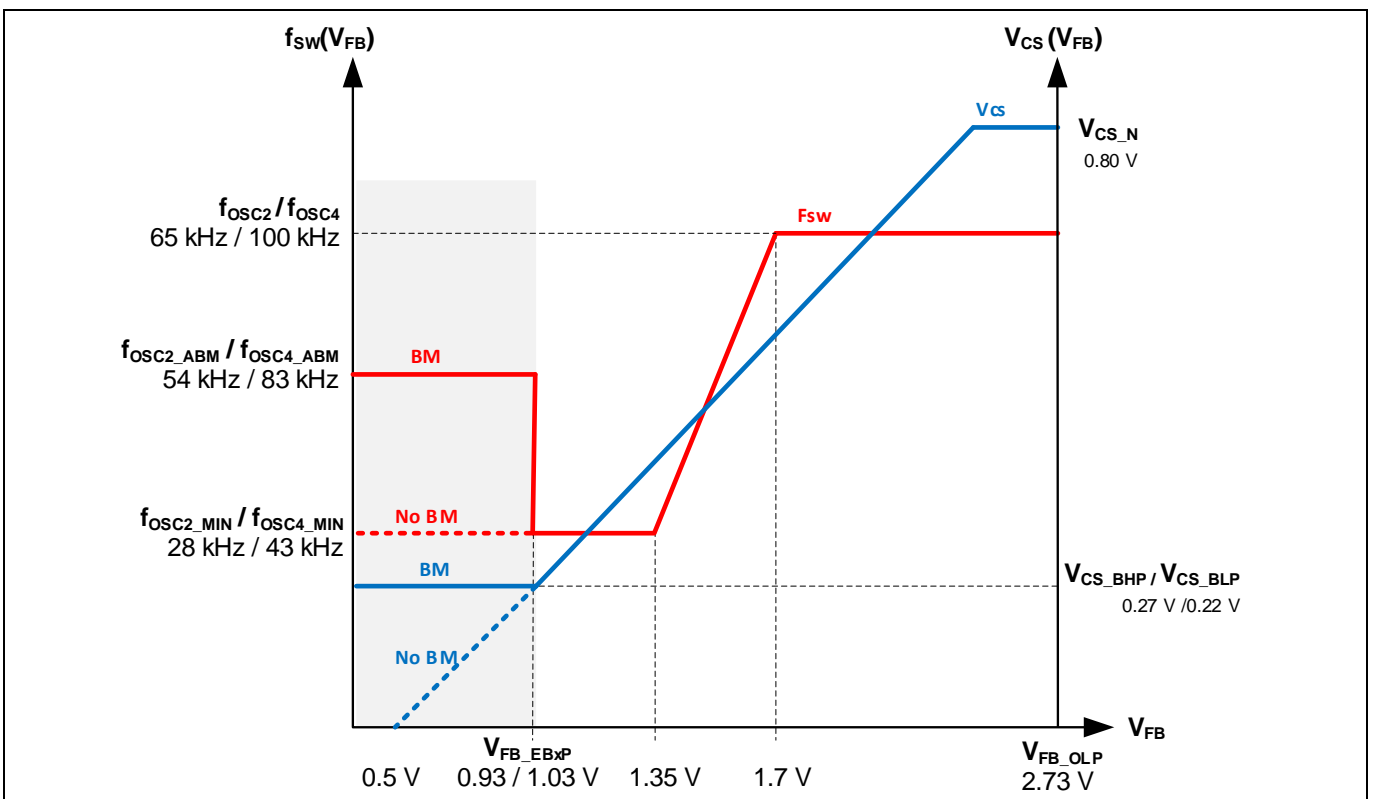
If the voltage at the current sense pin is lower than the preset threshold  $V_{CS\_STG}$  after the time  $t_{CS\_STG\_SAM}$  for three consecutive pulses during on-time of the power switch, this abnormal  $V_{CS}$  triggers the IC into auto restart mode.

### 3.3.3 Frequency reduction

Frequency reduction is implemented in ICE5xRxxxxZ to achieve a better efficiency during the light load. At light load, the reduced switching frequency  $F_{SW}$  improves efficiency by reducing the switching losses.

When the load decreases,  $V_{FB}$  decreases as well.  $F_{SW}$  is dependent on the  $V_{FB}$  as shown in **Figure 9**. Therefore,  $F_{SW}$  decreases as the load decreases.

For example,  $F_{SW}$  at high load is 65 kHz and starts to decrease at  $V_{FB} = 1.7$  V. There is no further frequency reduction once it reached the  $f_{OSC2\_MIN}$  even the load is further reduced.



**Figure 9** Frequency reduction curve

### 3.3.4 Slope compensation

ICE5xRxxxxZ can operate at continuous conduction mode (CCM). At CCM operation, a duty cycle greater than 50% may generate a subharmonic oscillation. To avoid the subharmonic oscillation, slope compensation is added to  $V_{CS}$  pin when the gate of the power MOSFET is turned on for more than 40% of the switching cycle period.

The relationship between  $V_{FB}$  and the  $V_{CS}$  for CCM operation is described in equation 4:

$$V_{FB} = V_{CS} \times G_{PWM} + V_{PWM} + M_{COMP} \times (T_{ON} - 40\% \times T_{PERIOD}) \quad (4)$$

where:

$T_{ON}$  : Gate turn on time of the power MOSFET

### Functional description

$M_{COMP}$  : Slope compensation rate

$T_{PERIOD}$  : Switching cycle period

Slope compensation circuit is disabled and no slope compensation is added into the  $V_{CS}$  pin during Active Burst mode to save the power consumption.

### 3.3.5 Oscillator and frequency jittering

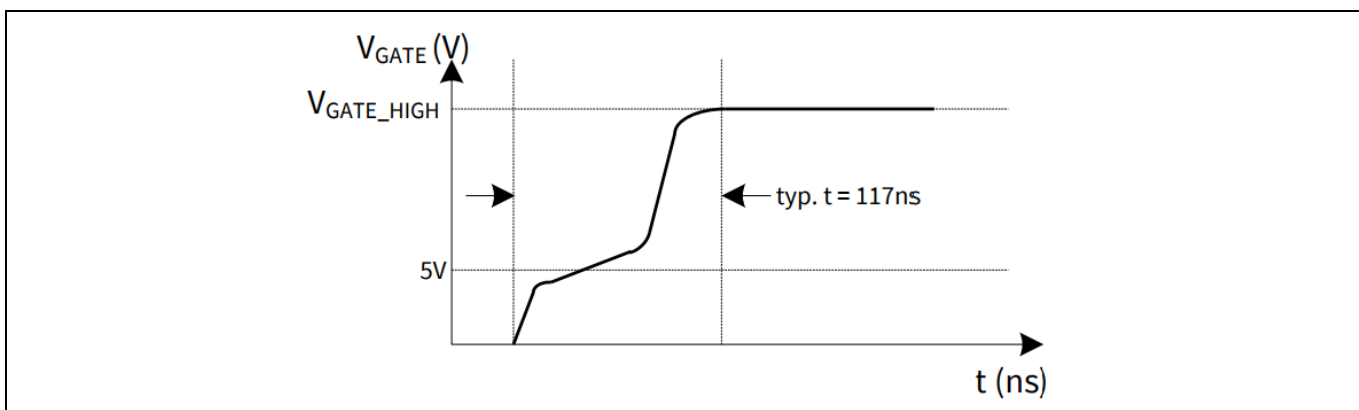
The oscillator generates a frequency of 65 kHz / 100 kHz with frequency jittering of  $\pm 4\%$  at a jittering period of  $T_{JITTER}$  (4 ms). The frequency jittering helps to reduce conducted EMI.

A capacitor, a current source, and a current sink that determine the frequency are integrated. The charging and discharging current of the implemented oscillator capacitor are internally trimmed to achieve a highly accurate switching frequency.

Once the soft start period is over and when the IC goes into normal operating mode, the frequency jittering is enabled. There is also frequency jittering during frequency reduction.

### 3.3.6 Modulated gate drive

The drive-stage is optimized for EMI consideration. The switch-on speed is slowed down before it reaches the CoolMOS™ turn on threshold. That is a slope control of the rising edge at the output of the driver (see [Figure 10](#)). Thus the leading switch spike during turn on is minimized.



**Figure 10** Gate rising waveform

### 3.4 Peak current limitation

There is a cycle-by-cycle peak current limitation realized by the current limit comparator to provide primary over-current protection. The primary current generates a voltage  $V_{CS}$  across the current sense resistor  $R_{CS}$  connected between the CS pin and the GND pin. If the voltage  $V_{CS}$  exceeds an internal voltage limit  $V_{CS,N}$ , the comparator immediately turns off the gate drive.

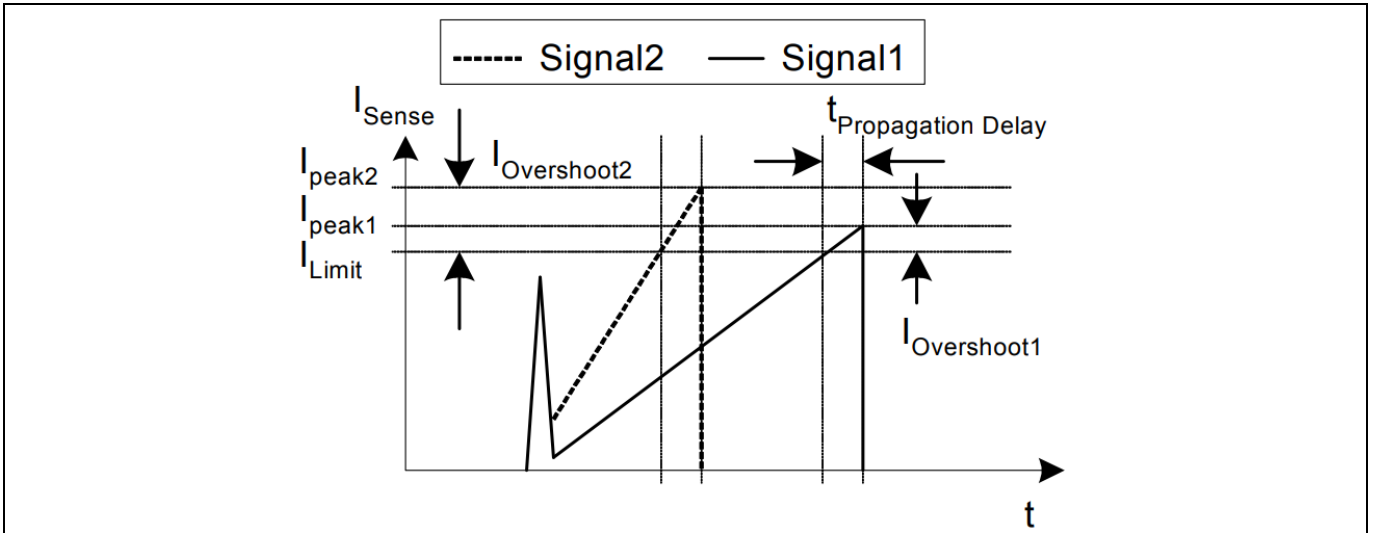
The primary peak current  $I_{PEAK\_PRI}$  can be calculated as below:

$$I_{PEAK\_PRI} = V_{CS,N} / R_{CS} \quad (5)$$

To avoid mistriggering caused by the MOSFET switch on transient voltage spikes, a leading edge-blanking time ( $t_{CS\_LEB}$ ) is integrated in the current sensing path.

### 3.4.1 Propagation delay compensation

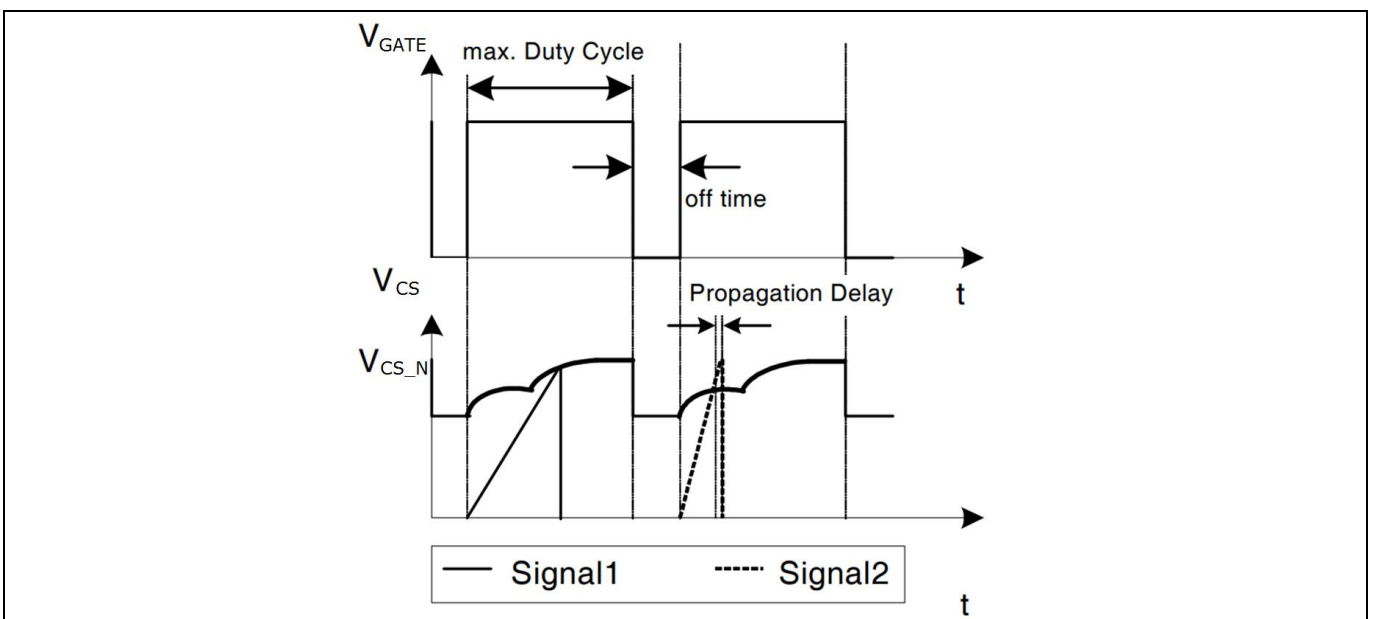
In case of an overcurrent detection, there is always a propagation delay from sensing the  $V_{CS}$  to switching the power MOSFET off. An overshoot on the peak current  $I_{peak}$  caused by the delay depends on the ratio of  $di/dt$  of the primary current (see [Figure 11](#)).



**Figure 11** Current limiting

The overshoot of Signal2 is larger than Signal1 due to the steeper rising waveform. This change in the slope is depending on the AC input voltage. Propagation delay compensation is integrated to reduce the overshoot due to  $di/dt$  of the rising primary current. Thus the propagation delay time between exceeding the current sense threshold  $V_{CS\_N}$  and the switching off of the power MOSFET is compensated over wide bus voltage range. Current limiting becomes more accurate, which results in a minimum difference of overload protection triggering power between low and high AC line input voltage.

Under CCM operation, the same  $V_{CS}$  do not result in the same power. To achieve a close overload triggering level for CCM, ICE5xRxxxxxZ has implemented a two compensation curve as shown [Figure 12](#). One of the curve is used for  $T_{ON}$  greater than 0.40 duty cycle and the other is for lower than 0.40 duty cycle.



**Figure 12** Dynamic voltage threshold  $V_{CS\_N}$

Similarly, the same concept of propagation delay compensation is also implemented in ABM with reduced level. With this implementation, the entry and exit Burst mode power can be close between low and high AC line input voltage.

### **3.5 Active burst mode with selectable power level**

At light load condition, the IC enters Active Burst mode (ABM) operation to minimize the power consumption. Details about the ABM operation are explained in the following paragraphs.

#### **3.5.1 Entering ABM operation**

The system enters into ABM operation when the two conditions below are met:

- The FB voltage is lower than the threshold of  $V_{FB\_EBLP}/V_{FB\_EBHP}$ , depending on the burst configuration option setup.
- A certain blanking time  $t_{FB\_BEB}$ .

Once all of these conditions are fulfilled, the ABM flip-flop is set and the controller enters ABM operation. This multicondition determination for entering ABM operation prevents mis-triggering of entering ABM operation, so that the controller enters ABM operation only when the output power is really low.

#### **3.5.2 During ABM operation**

After entering ABM, the PWM section is inactive, making the  $V_{OUT}$  start to decrease. As the  $V_{OUT}$  decreases,  $V_{FB}$  rises. Once  $V_{FB}$  exceeded  $V_{FB\_BOH}$ , the internal circuit is again activated by the internal bias to start with the switching.

If the PWM is still operating and the output load is still low,  $V_{OUT}$  increases and  $V_{FB}$  signal starts to decrease. When  $V_{FB}$  reaches the low threshold  $V_{FB\_BOF}$ , the internal bias is reset again and the PWM section is disabled with no switching until  $V_{FB}$  increases back to exceed  $V_{FB\_BOH}$  threshold.

In ABM,  $V_{FB}$  is like a sawtooth waveform swinging between  $V_{FB\_BOF}$  and  $V_{FB\_BOH}$  shown in [Figure 13](#).

During ABM, the peak current  $I_{PEAK\_ABM}$  of the power MOSFET is defined by:

$$I_{PEAK\_ABM} = V_{CS\_BXP}/R_{CS} \quad (6)$$

where  $V_{CS\_BXP}$  is the peak current limitation in ABM.

#### **3.5.3 Leaving ABM operation**

The FB voltage immediately increases if there is a sudden increase in the output load. When  $V_{FB}$  exceeds  $V_{FB\_LB}$ , it leaves ABM and the peak current limitation threshold voltage returns back to  $V_{CS\_N}$  immediately.

Functional description

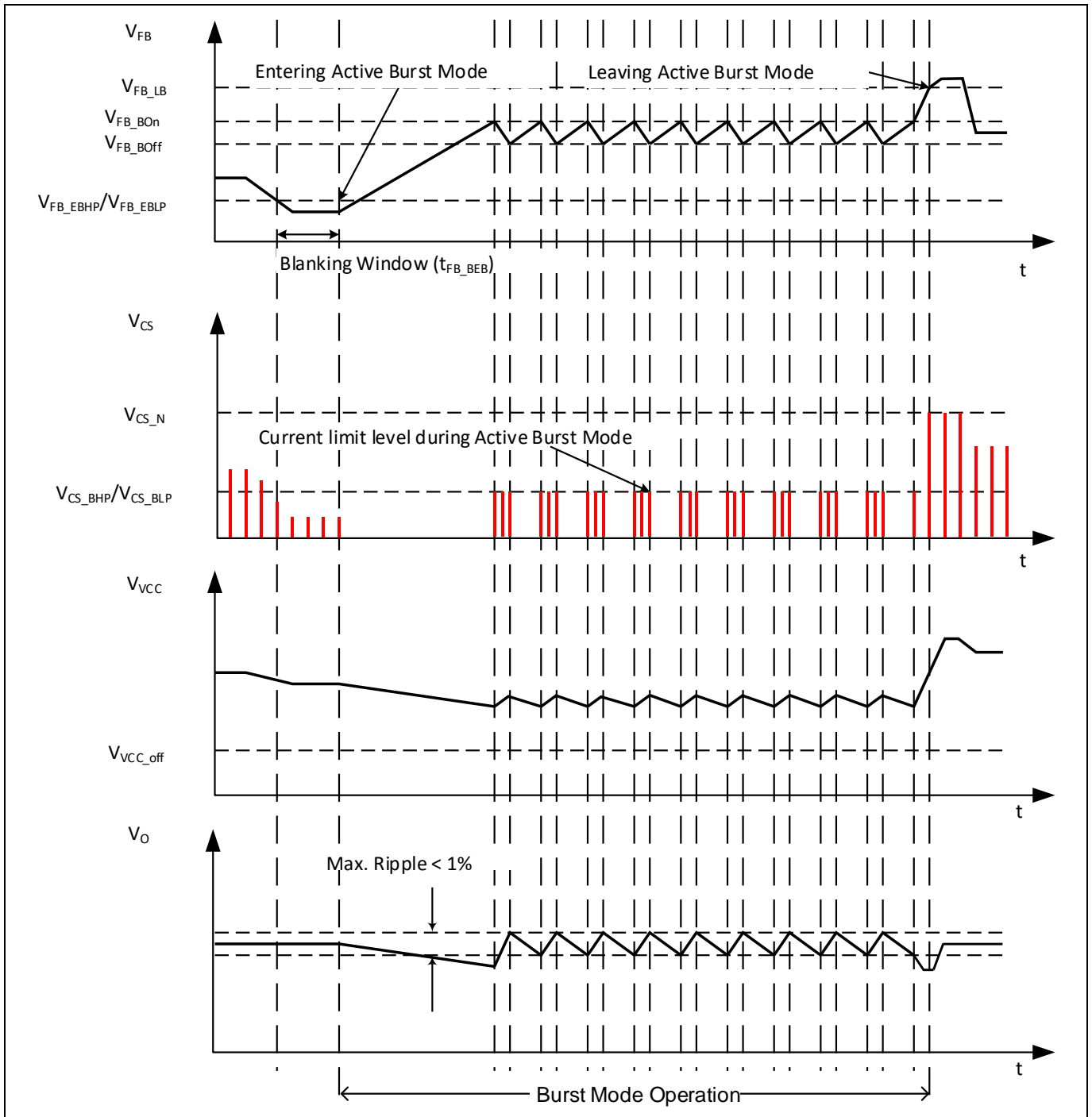


Figure 13 Signals in ABM

**Functional description**

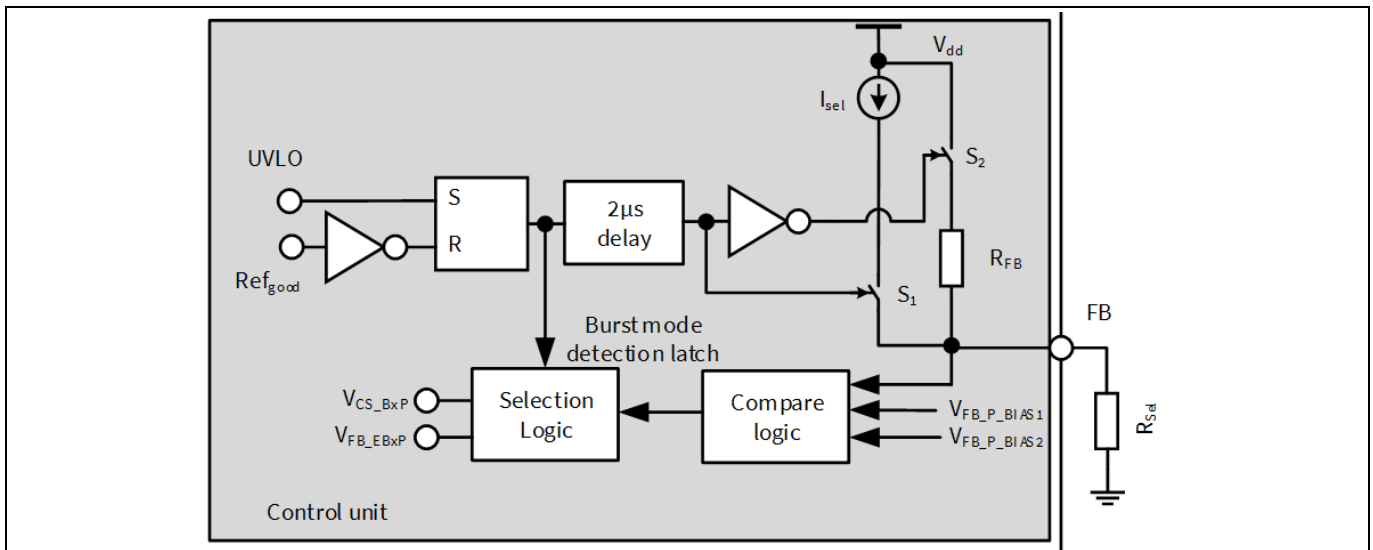
**3.5.4 ABM configuration**

The burst mode entry level can be selected by changing the different resistance  $R_{Sel}$  at FB pin. There are three configuration options depending on  $R_{Sel}$ , which corresponds to the options of no ABM (option 1), low range of ABM power (option 2) and high range of ABM power (option 3). The table below shows the control logic for the entry and exit level with the FB voltage.

**Table 4 ABM configuration option setup**

Option	$R_{Sel}$	$V_{FB}$	$V_{CS\_BxP}$	Entry level	Exit level
				$V_{FB\_EBxP}$	$V_{FB\_LB}$
1	< 470 kΩ	$V_{FB} < V_{FB\_P\_BIAS1}$	-	No ABM	No ABM
2	720 kΩ ~ 790 kΩ	$V_{FB\_P\_BIAS1} < V_{FB} < V_{FB\_P\_BIAS2}$	0.22 V	0.93 V	2.73 V
3 (default)	> 1210 kΩ	$V_{FB} > V_{FB\_P\_BIAS2}$	0.27 V	1.03 V	2.73 V

During IC first startup, the controller preset the ABM selection to option 3, the FB resistor ( $R_{FB}$ ) is turned off by internal switch  $S_2$  (see **Figure 14**) and a current source  $I_{sel}$  is turned on instead. From  $V_{CC} = 4.44$  V to  $V_{CC}$  on threshold, the FB pin starts to charge resistor  $R_{Sel}$  with current  $I_{sel}$  to a certain voltage level. When  $V_{CC}$  reaches  $V_{CC}$  on threshold, the FB voltage is sensed. The burst mode option is then chosen according to the FB voltage level. After finishing the selection, any change on the FB level does not change the burst mode option and the current source ( $I_{sel}$ ) is turned off while the FB resistor ( $R_{FB}$ ) is connected back to the circuit (**Figure 14**).



**Figure 14 ABM detect and adjust**

**3.6 Non-isolated/isolated configuration**

ICE5xRxxxxBZ has a VERR pin, which is connected to the input of an integrated error amplifier to support a non-isolated converter (see **Figure 2**). When  $V_{CC}$  is charging and before reaching the  $V_{CC}$  on threshold, a current source  $I_{ERR\_P\_BIAS}$  from the VERR pin together with  $R_{F1}$  and  $R_{F2}$  generates a voltage across it. If the VERR voltage is more than  $V_{ERR\_P\_BIAS}$  (0.2 V), non-isolated configuration is selected, otherwise, isolated configuration is selected. In an isolated configuration, the error amplifier output is disconnected from the FB pin.

In case of non-isolated configuration, the voltage divider  $R_{F1}$  and  $R_{F2}$  are used to sense the output voltage and compared with the internal reference voltage  $V_{ERR\_REF}$ . The difference between the sensed voltage and the



reference voltage is converted as an output current by the error amplifier. The output current charges or discharges the resistor and capacitor network connected at the FB pin for the loop compensation.

### 3.7 Protection functions

The ICE5xRxxxxxZ provides numerous protection functions that considerably improve the power supply system robustness, safety, and reliability. The following table summarizes these protection functions and the corresponding protection mode whether as a non-switch auto restart, auto restart or odd skip auto restart mode. Refer to [Figure 15](#), [Figure 16](#) and [Figure 17](#) for the waveform illustration of protection modes.

**Table 5 Protection functions**

Protection functions	Normal mode	Burst mode		Protection mode
		Burst ON	Burst OFF	
Line overvoltage (CZ version)	√	√	√	Non-switch auto restart
$V_{CC}$ overvoltage	√	√	n/a <sup>1</sup>	Odd skip auto restart
$V_{CC}$ undervoltage	√	√	√	Auto restart
Overload or open loop	√	n/a <sup>1</sup>	n/a <sup>1</sup>	Odd skip auto restart
Overtemperature	√	√	√	Non-switch auto restart
$V_{CC}$ short to GND	√	√	√	No startup

#### 3.7.1 Line overvoltage (CZ version)

The AC line overvoltage protection (LOVP) is detected by the sensing bus capacitor voltage through the VIN pin via the voltage divider resistors,  $R_{I1}$  and  $R_{I2}$  ([Figure 1](#)). Once the  $V_{VIN}$  voltage is higher than the line overvoltage threshold ( $V_{VIN\_LOVP}$ ), the controller enters into protection mode until  $V_{VIN}$  is lower than  $V_{VIN\_LOVP}$ . This protection can be disabled by connecting the VIN pin to GND.

#### 3.7.2 $V_{CC}$ overvoltage and undervoltage

During operation, the  $V_{CC}$  voltage is continuously monitored. If  $V_{CC}$  is either below  $V_{VCC\_OFF}$  for 50  $\mu$ s ( $t_{VCC\_OFF\_B}$ ) or above  $V_{VCC\_OVP}$  for 55  $\mu$ s ( $t_{VCC\_OVP\_B}$ ), the power MOSFET is kept switch off. After the  $V_{CC}$  voltage falls below the threshold  $V_{VCC\_OFF}$ , the new startup sequence is activated. The  $V_{CC}$  capacitor is then charged up. Once the voltage exceeds the threshold  $V_{VCC\_ON}$ , the IC begins to operate with a new soft start.

#### 3.7.3 Overload or open loop

In case of open control loop or output overload, the FB voltage is pulled up. When  $V_{FB}$  exceeds  $V_{FB\_OLP}$  after a blanking time of  $t_{FB\_OLP\_B}$ , the IC enters odd skip auto restart mode. The blanking time enables the converter to provide a peak power in case the increase in  $V_{FB}$  is due to a sudden load increase.

#### 3.7.4 Overtemperature

If the junction temperature of the controller exceeds  $T_{JCON\_OTP}$ , the IC enters into overtemperature protection (OTP) auto restart mode. The IC has also implemented with a 40°C hysteresis. That means the IC can only be recovered from OTP when the controller junction temperature is dropped 40°C lower than the overtemperature trigger point.

<sup>1</sup> Not applicable.

### 3.7.5 V<sub>CC</sub> short to GND

To limit the power dissipation of the startup circuit at V<sub>CC</sub> short to GND condition, the V<sub>CC</sub> charging current is limited to a minimum level of I<sub>VCC\_Charge1</sub>. With such low current, the power loss of the IC is limited to prevent overheating.

### 3.7.6 Protection modes

All the protections are in auto restart mode with a new soft start sequence. The three auto restart modes are illustrated in the following figures.

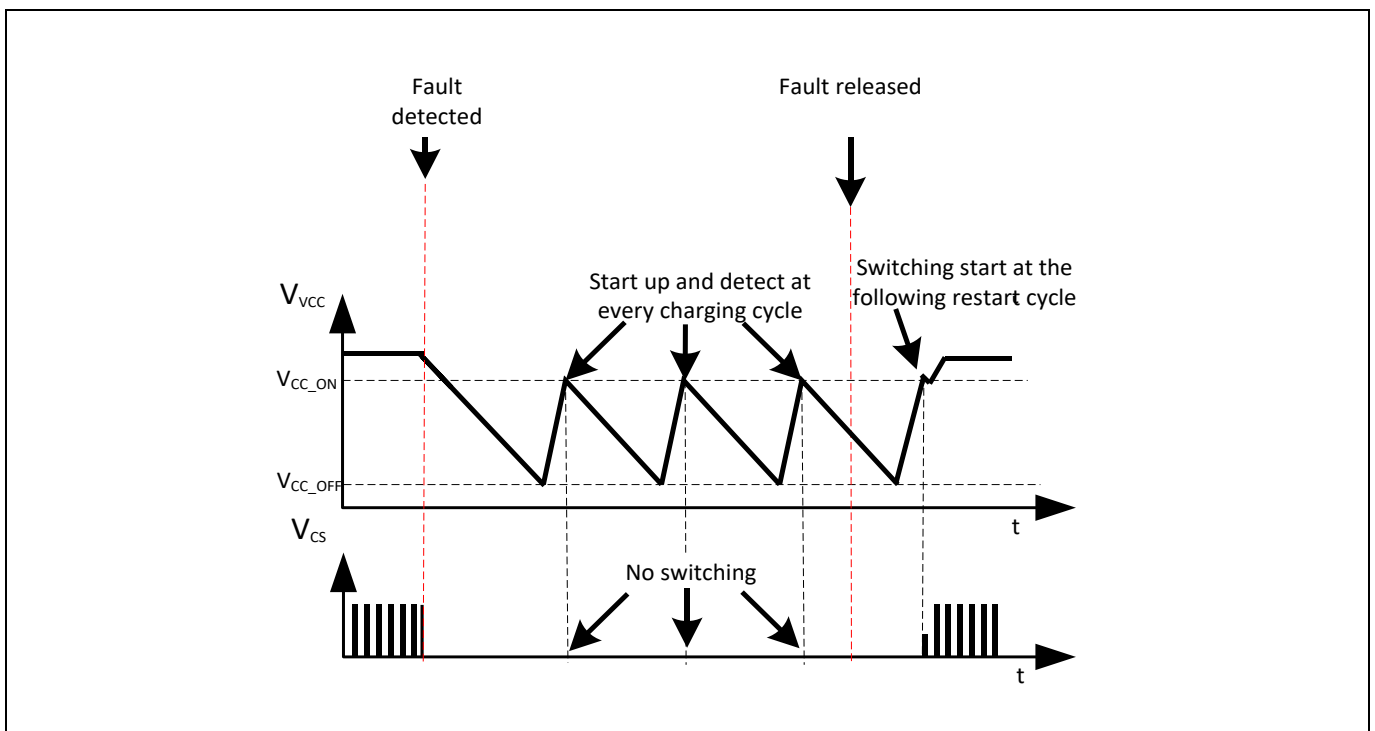


Figure 15 Non-switch auto restart mode

Functional description

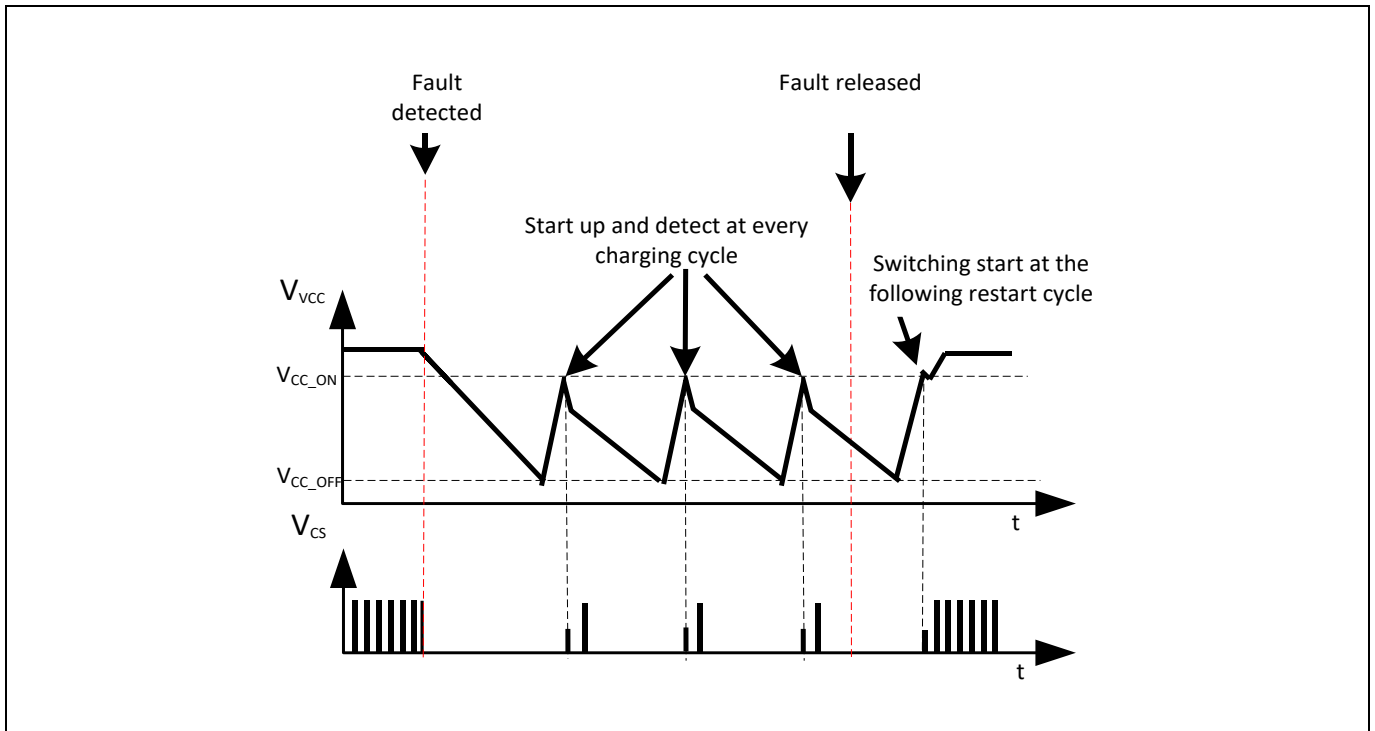


Figure 16 Auto restart mode

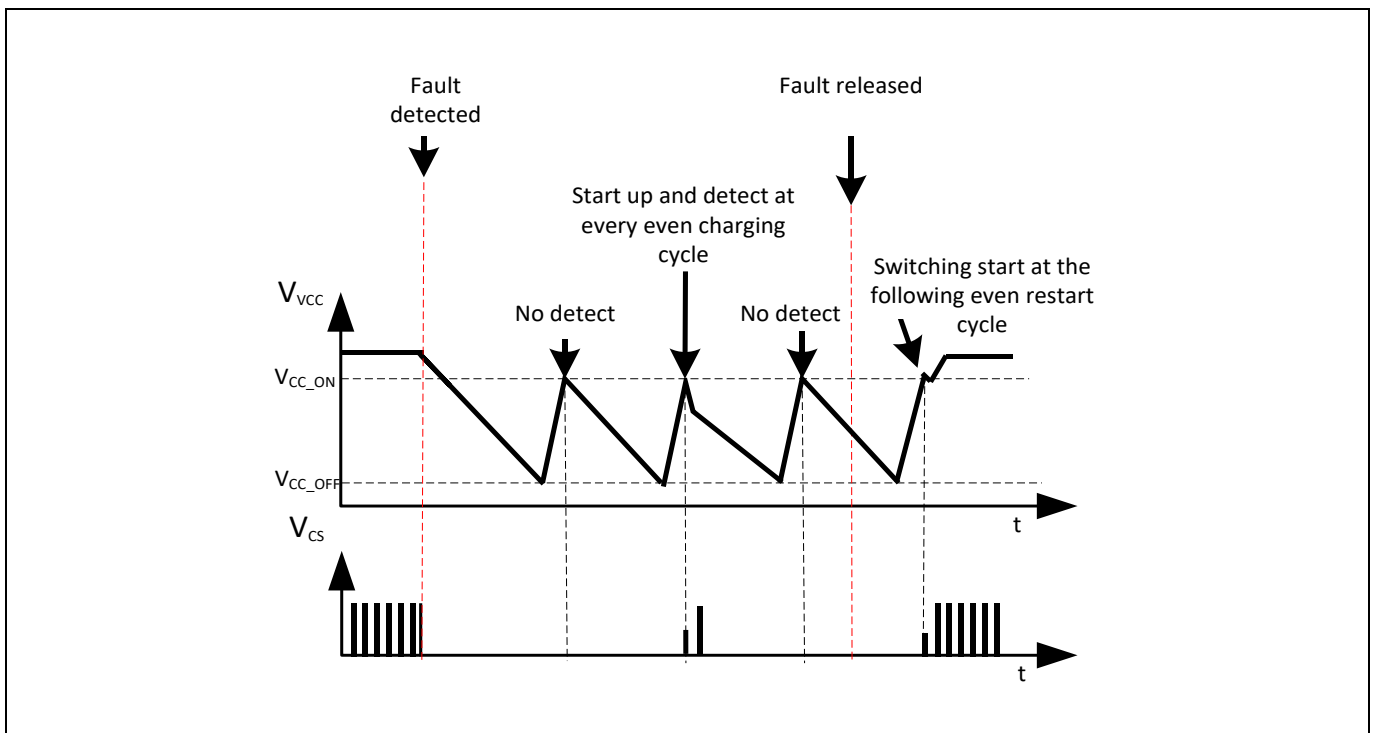


Figure 17 Odd skip auto restart

## 4 Electrical characteristics

**Attention:** All voltages are measured with respect to ground (pin 8). The voltage levels are valid if other ratings are not violated.

### 4.1 Absolute maximum ratings

**Attention:** Stresses above the maximum values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding any one of these values may cause irreversible damage to the integrated circuit. For the same reason, make sure that any capacitor that is connected to pin 7 (VCC) is discharged before assembling the application circuit.  $T_a = 25^\circ\text{C}$  unless otherwise specified.

**Table 6** Absolute maximum ratings

Parameter	Symbol	Limit values		Unit	Note or test condition
		Min.	Max.		
Drain voltage ICE5xRxx80xZ ICE5xR3995xZ	$V_{\text{DRAIN}}$	800 950	– –	V	$T_j = 25^\circ\text{C}$
Pulse drain current ICE5xR3995xZ ICE5BR4780BZ ICE5xR2280xZ	$I_{\text{D,Pulse}}$	– – –	5.0 <sup>1</sup> 2.6 <sup>1</sup> 5.8 <sup>2</sup>	A	
Avalanche energy, repetitive, $t_{\text{AR}}$ limited by maximal $T_j = 150^\circ\text{C}$ and $T_{j,\text{Start}} = 25^\circ\text{C}$ ICE5xR2280xZ ICE5BR4780BZ ICE5xR3995xZ	$E_{\text{AR}}$	– – –	0.05 0.02 0.04	mJ	$I_{\text{D}} = 0.40\text{ A}, V_{\text{DD}} = 50\text{ V}$ $I_{\text{D}} = 0.20\text{ A}, V_{\text{DD}} = 50\text{ V}$ $I_{\text{D}} = 0.20\text{ A}, V_{\text{DD}} = 50\text{ V}$
Avalanche current, repetitive, $t_{\text{AR}}$ limited by maximal $T_j = 150^\circ\text{C}$ and $T_{j,\text{Start}} = 25^\circ\text{C}$ ICE5BR4780BZ ICE5xR3995xZ ICE5xR2280xZ	$I_{\text{AR}}$	– – –	0.20 0.20 0.40	A	
VCC supply voltage	$V_{\text{CC}}$	-0.3	27.0	V	
GATE voltage	$V_{\text{GATE}}$	-0.3	27.0	V	
FB voltage	$V_{\text{FB}}$	-0.3	3.6	V	
VERR voltage	$V_{\text{ERR}}$	-0.3	3.6	V	
CS voltage	$V_{\text{CS}}$	-0.3	3.6	V	
VIN voltage	$V_{\text{VIN}}$	-0.3	3.6	V	
Maximum DC current on any pin		-10.0	10.0	mA	Except DRAIN and CS pin.

<sup>1</sup> Pulse width  $t_{\text{p}}$  limited by  $T_{j,\text{max}}$ .

<sup>2</sup> Pulse width  $t_{\text{p}} = 20\ \mu\text{s}$  and limited by  $T_{j,\text{max}}$ .

**Electrical characteristics**

Parameter	Symbol	Limit values		Unit	Note or test condition
		Min.	Max.		
ESD robustness HBM	$V_{ESD\_HBM}$	–	2000	V	According to EIA/JESD22.
ESD robustness CDM	$V_{ESD\_CDM}$	–	500	V	
Junction temperature range	$T_j$	-40	150	°C	Controller and CoolMOS™.
Storage temperature	$T_{STORE}$	-55	150	°C	
Thermal resistance (junction-ambient)	$R_{thJA}$			K/W	Setup according to the JEDEC standard JESD51 and using minimum drain pin copper area in a 2 oz copper single-sided PCB.
ICE5BR4780BZ		–	107		
ICE5XR3995xZ		–	106		
ICE5XR2280xZ		–	104		

## 4.2 Operating range

Note: Within the operating range, the IC operates as described in the functional description.

**Table 7 Operating range**

Parameter	Symbol	Limit values		Unit	Note or test condition
		Min.	Max.		
VCC supply voltage	$V_{VCC}$	$V_{VCC\_OFF}$	$V_{VCC\_OVP}$		
Junction temperature of controller	$T_{jCon\_op}$	-40	$T_{jCon\_OTP}$	°C	Maximum value limited due to OTP of controller chip.
Junction temperature of CoolMOS™	$T_{jCoolMOS\_op}$	-40	150	°C	

## 4.3 Operating conditions

Note: The electrical characteristics involve the spread of values within the specified supply voltage and junction temperature range  $T_j$  from –40°C to 125°C. Typical values represent the median values, which are related to 25°C. If not otherwise stated, a supply voltage of  $V_{CC} = 18\text{ V}$  is assumed.

**Table 8 Operating conditions**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
VCC charge current	$I_{VCC\_Charge1}$	-0.35	-0.20	-0.09	mA	$V_{VCC} = 0\text{ V}$ , $R_{StartUp} = 50\text{ M}\Omega$ and $V_{DRAIN} = 90\text{ V}$
	$I_{VCC\_Charge2}$	–	-3.2	–	mA	$V_{VCC} = 3\text{ V}$ , $R_{StartUp} = 50\text{ M}\Omega$ and $V_{DRAIN} = 90\text{ V}$
	$I_{VCC\_Charge3}$	-5	-3	-1	mA	$V_{VCC} = 15\text{ V}$ , $R_{StartUp} = 50\text{ M}\Omega$ and $V_{DRAIN} = 90\text{ V}$
Current consumption, startup current	$I_{VCC\_Startup}$	–	0.25	–	mA	$V_{VCC} = 15\text{ V}$
Current consumption, normal with Inactive Gate	$I_{VCC\_Normal1}$	–	0.9	–	mA	$I_{FB} = 0\text{ A}$

**Electrical characteristics**

Parameter	Symbol	Limit values			Unit	Note or test Condition
		Min.	Typ.	Max.		
Current consumption, normal with Active Gate	$I_{VCC\_Normal2}$				mA	
ICE5BR2280BZ		–	–	1.89		
ICE5BR3995xZ		–	–	1.82		
ICE5AR3995BZ		–	–	2.21		
ICE5BR4780BZ		–	–	1.69		
ICE5AR2280CZ		–	–	2.31		
Current consumption, auto restart	$I_{VCC\_AR}$	–	410	–	μA	
Current consumption, Burst mode – isolated	$I_{VCC\_Burst Mode\_ISO}$	–	0.54	–	mA	
Current consumption, Burst mode – non-isolated	$I_{VCC\_Burst Mode\_NISO}$	–	0.61	–	mA	
VCC turn-on threshold voltage	$V_{VCC\_ON}$	15.3	16.0	16.5	V	
VCC turn-off threshold voltage	$V_{VCC\_OFF}$	9.4	10.0	10.4	V	
VCC short circuit protection	$V_{VCC\_SCP}$	–	1.1	1.9	V	
VCC turn-off blanking	$t_{VCC\_OFF\_B}$	–	50	–	μs	

#### 4.4 Internal voltage reference

**Table 9 Internal voltage reference**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Internal reference voltage	$V_{REF}$	3.20	3.30	3.39	V	Measured at FB pin $I_{FB} = 0$ A

#### 4.5 PWM section

**Table 10 PWM section**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Fixed oscillator frequency – 100 kHz	$f_{OSC3}$	92	100	108	kHz	
	$f_{OSC4}$	94	100	106	kHz	$T_j = 25^\circ\text{C}$
Fixed oscillator frequency – 100 kHz (ABM)	$f_{OSC4\_ABM}$	71	83	94	kHz	$T_j = 25^\circ\text{C}$
Fixed oscillator frequency – 100 kHz (minimum $F_{SW}$ )	$f_{OSC4\_MIN}$	36	43	51	kHz	$T_j = 25^\circ\text{C}$
Fixed oscillator frequency – 65 kHz	$f_{OSC1}$	59.8	65	70.2	kHz	
	$f_{OSC2}$	61.1	65	68.9	kHz	$T_j = 25^\circ\text{C}$
Fixed oscillator frequency – 65 kHz (ABM)	$f_{OSC2\_ABM}$	46.2	54	61.1	kHz	$T_j = 25^\circ\text{C}$

**Electrical characteristics**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Fixed oscillator frequency – 65 kHz (minimum $F_{sw}$ )	$f_{OSC2\_MIN}$	23.4	28	33.2	kHz	$T_j = 25^\circ\text{C}$
Frequency jittering range	$F_{JITTER}$	–	$\pm 4$	–	%	$T_j = 25^\circ\text{C}$
Frequency jittering period	$T_{JITTER}$	–	4	–	ms	$T_j = 25^\circ\text{C}$
Maximum duty cycle	$D_{MAX}$	70	75	80	%	
Feedback pull-up resistor	$R_{FB}$	11	15	20	k $\Omega$	
PWM-OP gain	$G_{PWM}$	1.91	2.03	2.16		
Offset for voltage ramp	$V_{PWM}$	0.42	0.50	0.58	V	
Slope compensation rate - 100 kHz	$M_{COMP}$	41	50	58	mV/ $\mu\text{s}$	$V_{cs} = 0\text{ V}$
Slope compensation rate - 65 kHz	$M_{COMP}$	26.5	32.5	38	mV/ $\mu\text{s}$	$V_{cs} = 0\text{ V}$

## 4.6 Error amplifier

**Table 11 Error amplifier**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Transconductance	$G_{ERR\_M}$	2.14	2.80	3.44	mA/V	
Transconductance – Burst mode	$G_{ERR\_BM}$	6.9	9.2	11.6	mA/V	
Error amplifier source current	$I_{ERR\_SOURCE}$	85	150	223	$\mu\text{A}$	
Error amplifier sink current	$I_{ERR\_SINK}$	85	150	223	$\mu\text{A}$	
Error amplifier reference voltage	$V_{ERR\_REF}$	1.76	1.80	1.84	V	
Error amplifier output dynamic range of transconductance	$V_{ERR\_DYN}$	0.05	–	3.15	V	
Error amplifier mode bias current	$I_{ERR\_P\_BIAS}$	9.5	14.0	18.5	$\mu\text{A}$	
Error amplifier mode threshold	$V_{ERR\_P\_BIAS}$	0.16	0.20	0.24	V	

## 4.7 Current sense

**Table 12 Current sense**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Peak current limitation in normal operation	$V_{CS\_N}$	0.72	0.80	0.88	V	$dV_{sense}/dt = 0.41\text{ V}/\mu\text{s}$
Peak current limitation in normal operation, 15% of $T_{ON}$	$V_{CS\_N15}$	0.74	0.79	0.84	V	
Leading edge-blanking time	$t_{CS\_LEB}$	70	220	365	ns	
Peak current limitation in ABM - high power	$V_{CS\_BHP}$	0.23	0.27	0.31	V	

**Electrical characteristics**

Peak current limitation in ABM - low power	$V_{CS\_BLP}$	0.18	0.22	0.26	V	
Abnormal CS voltage threshold	$V_{CS\_STG}$	0.06	0.10	0.15	V	
Abnormal CS voltage consecutive trigger	$P_{CS\_STG}$	–	3	–	cycle	
Abnormal CS voltage sample period	$t_{CS\_STG\_SAM}$	$t_{PERIOD} \times 0.36$	$t_{PERIOD} \times 0.4$	$t_{PERIOD} \times 0.44$	$\mu s$	

## 4.8 Soft start

**Table 13 Soft start**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Soft start time	$t_{SS}$	7.3	12.0	–	ms	
Soft start time step	$t_{SS\_S}^1$	–	3	–	ms	
CS peak voltage at first step of soft start	$V_{SS1}^1$	–	0.30	–	V	CS peak voltage.
Step increment of CS peak voltage in soft start	$V_{SS\_S}^1$	–	0.15	–	V	CS peak voltage.

## 4.9 Active burst mode

**Table 14 Active Burst mode**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Charging current to select burst mode	$I_{sel}$	2.5	3.0	3.5	$\mu A$	
Burst mode selection reference voltage threshold	$V_{FB\_P\_BIAS1}$	1.65	1.73	1.80	V	
Burst mode selection reference voltage threshold	$V_{FB\_P\_BIAS2}$	2.76	2.89	3.01	V	
Feedback voltage for entering ABM for high power	$V_{FB\_EBHP}$	0.98	1.03	1.08	V	
Feedback voltage for entering ABM for low power	$V_{FB\_EBLP}$	0.88	0.93	0.98	V	
Blanking time for entering ABM	$t_{FB\_BEB}$	–	36	–	ms	
Feedback voltage for leaving ABM	$V_{FB\_LB}$	2.63	2.73	2.83	V	
Feedback voltage for burst-on – isolated case	$V_{FB\_Bon\_ISO}$	2.26	2.35	2.45	V	
Feedback voltage for burst-off – isolated case	$V_{FB\_Boff\_ISO}$	1.88	2.00	2.05	V	

<sup>1</sup> Not subject to production test, specified by design.



**Electrical characteristics**

Feedback voltage for burst-on – non-isolated case	$V_{FB\_Bon\_NISO}$	1.88	1.95	2.05	V	
Feedback voltage for burst-off – non-isolated case	$V_{FB\_Boff\_NISO}$	1.50	1.55	1.64	V	

**4.10 Line overvoltage protection (CZ version)**
**Table 15 Line OVP**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Line overvoltage threshold	$V_{VIN\_LOVP}$	2.75	2.85	2.95	V	
Line overvoltage blanking	$t_{VIN\_LOVP\_B}$	–	250	–	µs	

**4.11  $V_{CC}$  overvoltage protection**
**Table 16  $V_{CC}$  overvoltage protection**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
VCC overvoltage threshold	$V_{VCC\_OVP}$	24.0	25.5	27.0	V	
VCC overvoltage blanking	$t_{VCC\_OVP\_B}$	–	55	–	µs	

**4.12 Overload protection**
**Table 17 Overload protection**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Overload detection threshold for OLP protection at FB pin	$V_{FB\_OLP}$	2.63	2.73	2.83	V	
Overload protection blanking time	$t_{FB\_OLP\_B}$	30	54	–	ms	

**4.13 Thermal protection**
**Table 18 Thermal protection**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Overtemperature protection	$T_{jcon\_OTP}^1$	129	140	150	°C	Junction temperature of the controller chip (not the CoolMOS™ chip).
Overtemperature hysteresis	$T_{jHYS\_OTP}$	–	40	–	°C	
Overtemperature blanking time	$T_{jcon\_OTP\_B}$	–	50	–	µs	

<sup>1</sup>Not subject to production test, specified by design.

### 4.14 CoolMOS™ section

**Table 19 ICE5xRxxxxxZ**

Parameter	Symbol	Limit values			Unit	Note or test condition
		Min.	Typ.	Max.		
Drain source breakdown voltage ICE5xRxx80xZ ICE5xR3995xZ	$V_{(BR)DSS}$	800 950	– –	– –	V	$T_j = 25^\circ\text{C}$
Drain source on-resistance (inclusive of low side MOSFET) ICE5BR4780BZ  ICE5xR2280xZ  ICE5xR3995xZ	$R_{DSon}$	– – – – –	4.13 8.69 <sup>1</sup> 2.13 4.31 <sup>1</sup> 3.46 7.69 <sup>1</sup>	4.85 – 2.35 – 4.05 –	$\Omega$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$ at $I_D = 0.4\text{ A}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$ at $I_D = 1\text{ A}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$ at $I_D = 0.8\text{ A}$
Effective output capacitance, energy related <sup>1</sup> ICE5BR4780BZ ICE5xR2280xZ ICE5xR3995xZ	$C_{o(er)}$	– – –	3 7 5	– – –	pF	$V_{GS} = 0\text{ V}, V_{DS} = 0 \sim 500\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 0 \sim 500\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 0 \sim 400\text{ V}$
Rise time	$t_{rise}^2$	–	30	–	ns	
Fall time	$t_{fall}^2$	–	30	–	ns	

<sup>1</sup>Not subject to production test, specified by design.

<sup>2</sup>Measured in a typical flyback / buck converter application.

## 5 CoolMOS™ performance characteristics

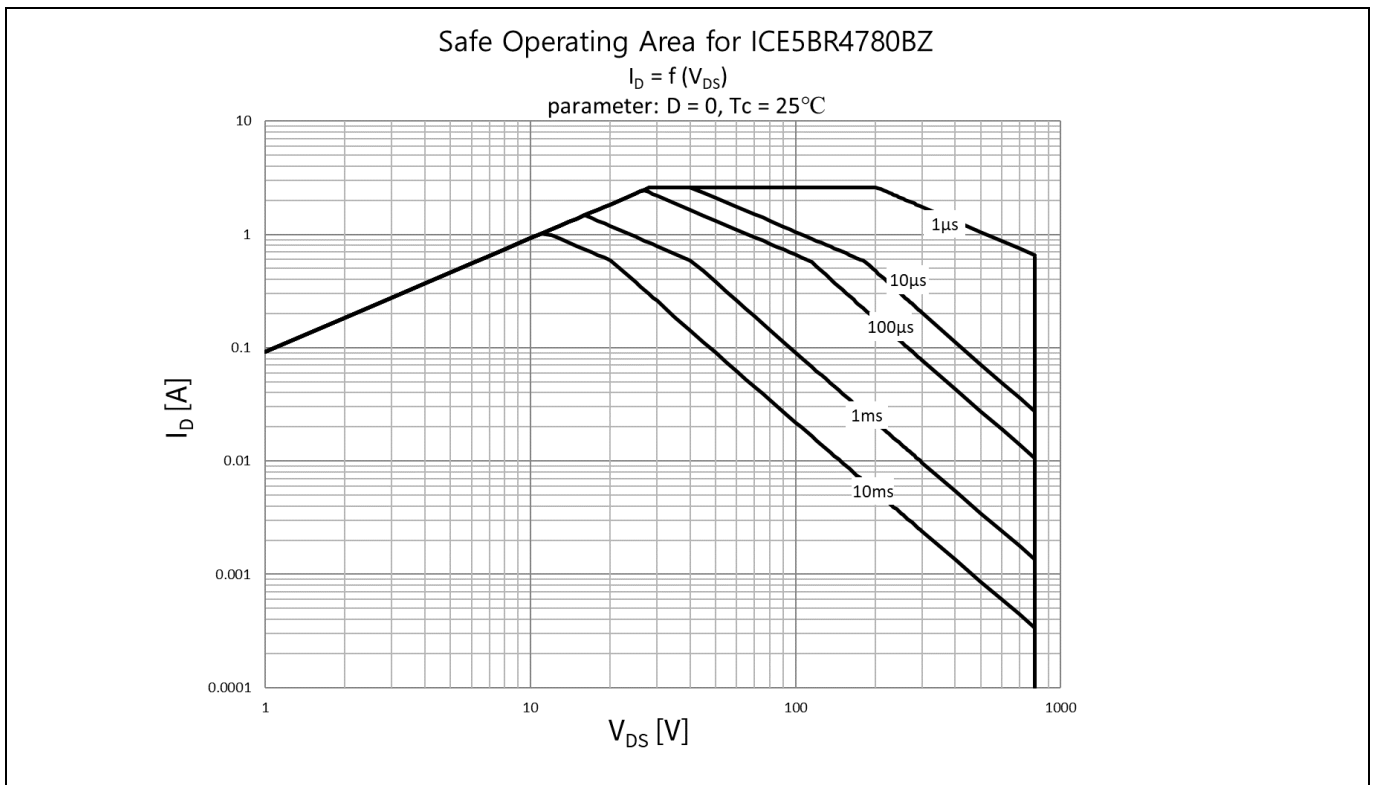


Figure 18 Safe operating area (SOA) curve for ICE5BR4780BZ

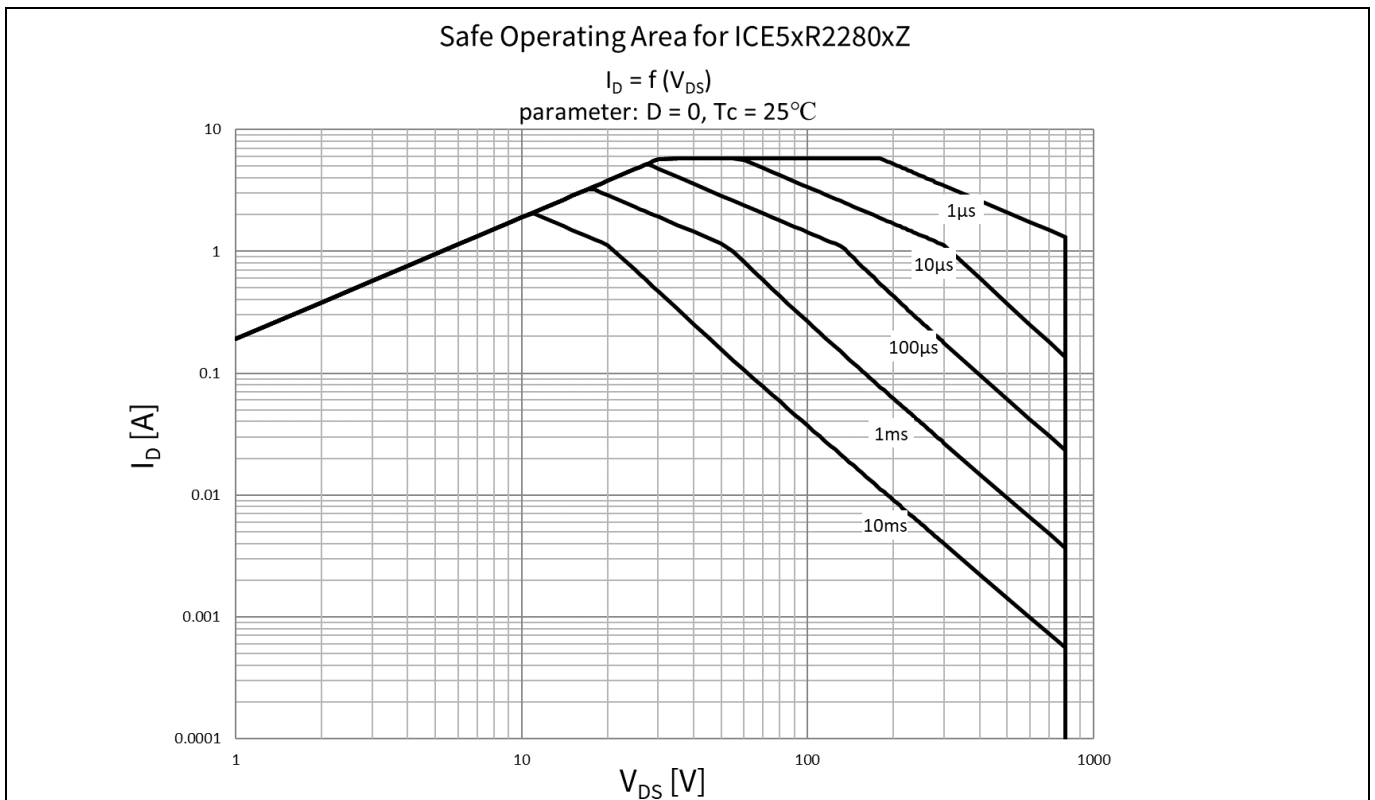


Figure 19 Safe operating area (SOA) curve for ICE5xR2280xZ

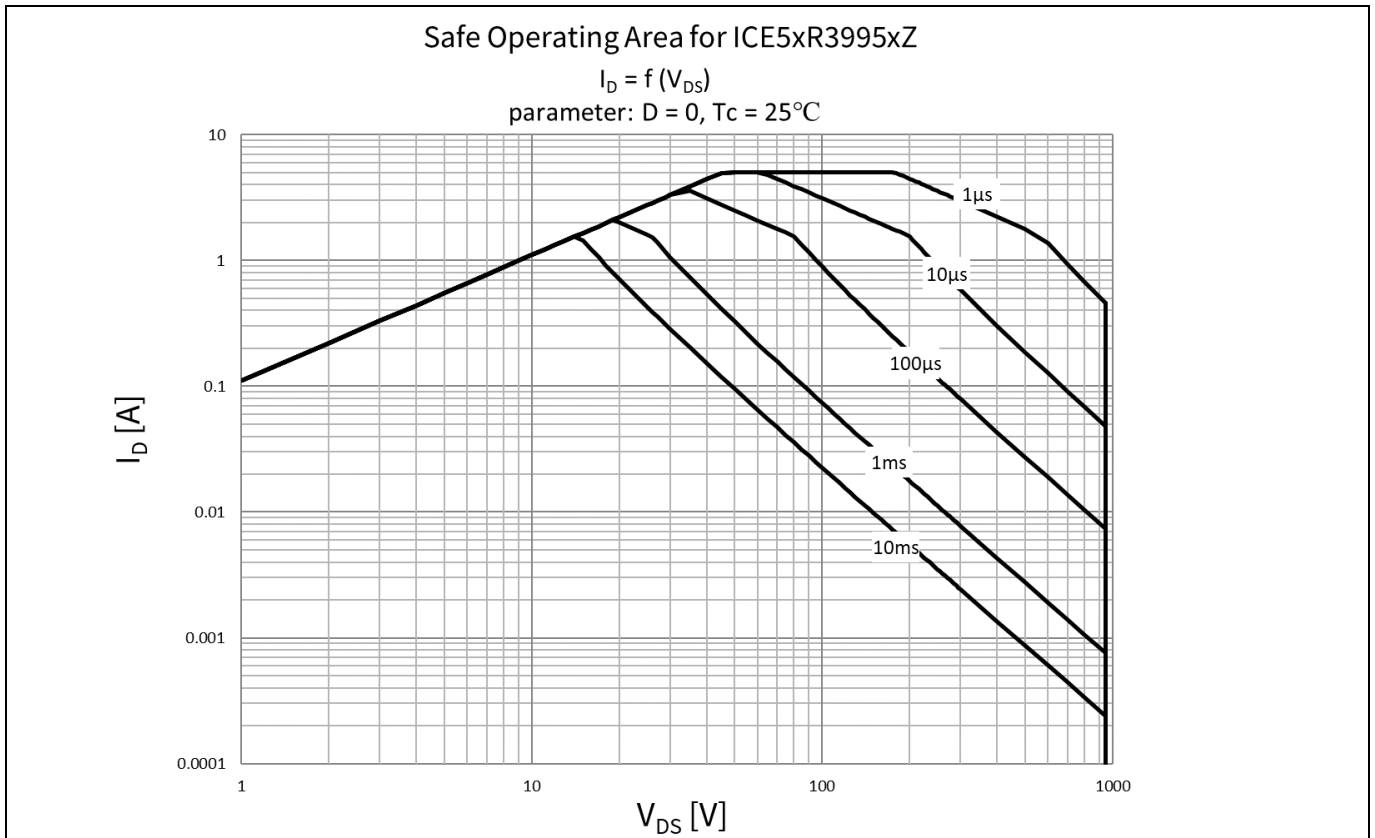


Figure 20 Safe operating area (SOA) curve for ICE5xR3995xZ

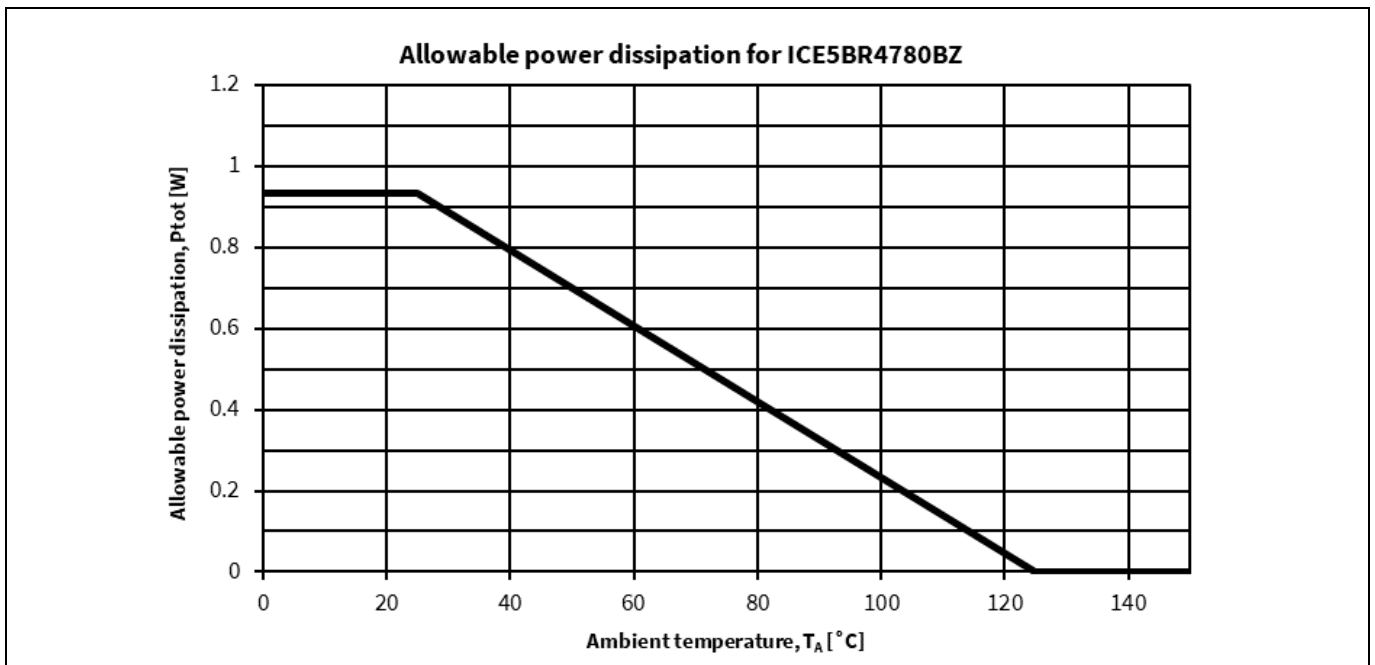


Figure 21 Power dissipation of ICE5BR4780BZ;  $P_{tot} = f(T_a)$  (Maximum ratings as given in chapter 4.1 must not be exceeded)

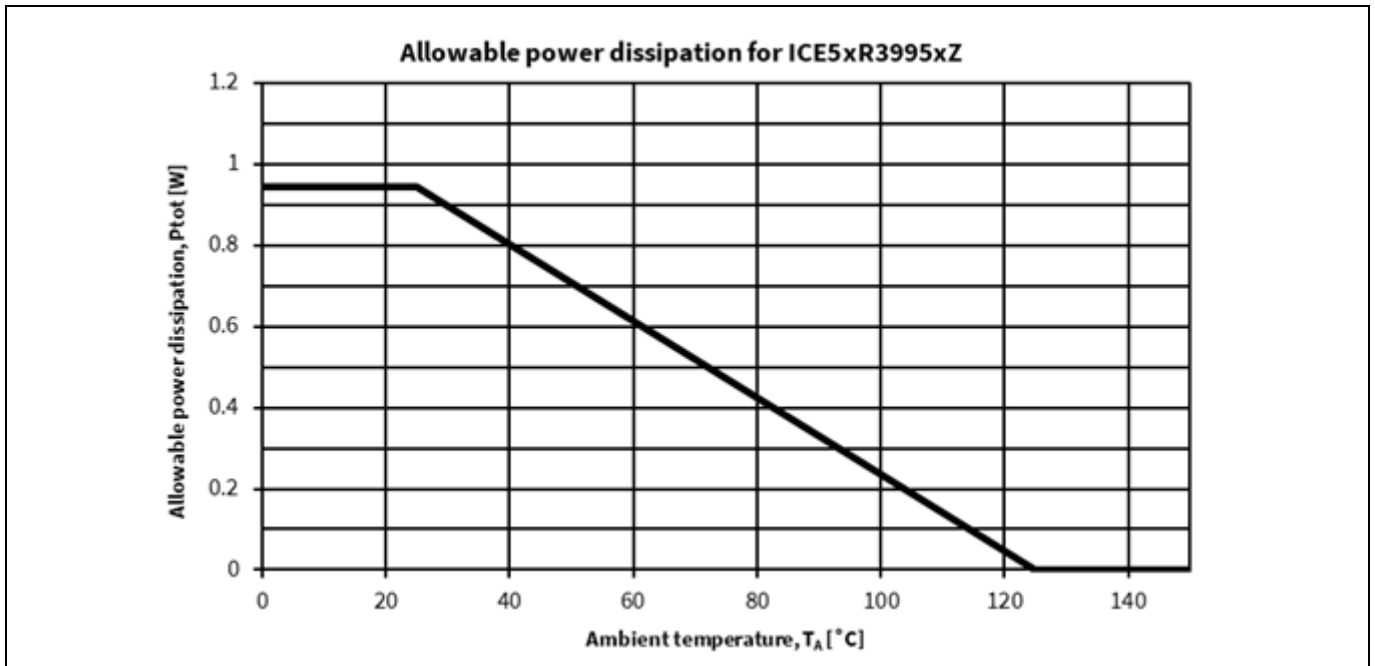


Figure 22 Power dissipation of ICE5xR3995xZ;  $P_{tot} = f(T_A)$  (Maximum ratings as given in chapter 4.1 must not be exceeded)

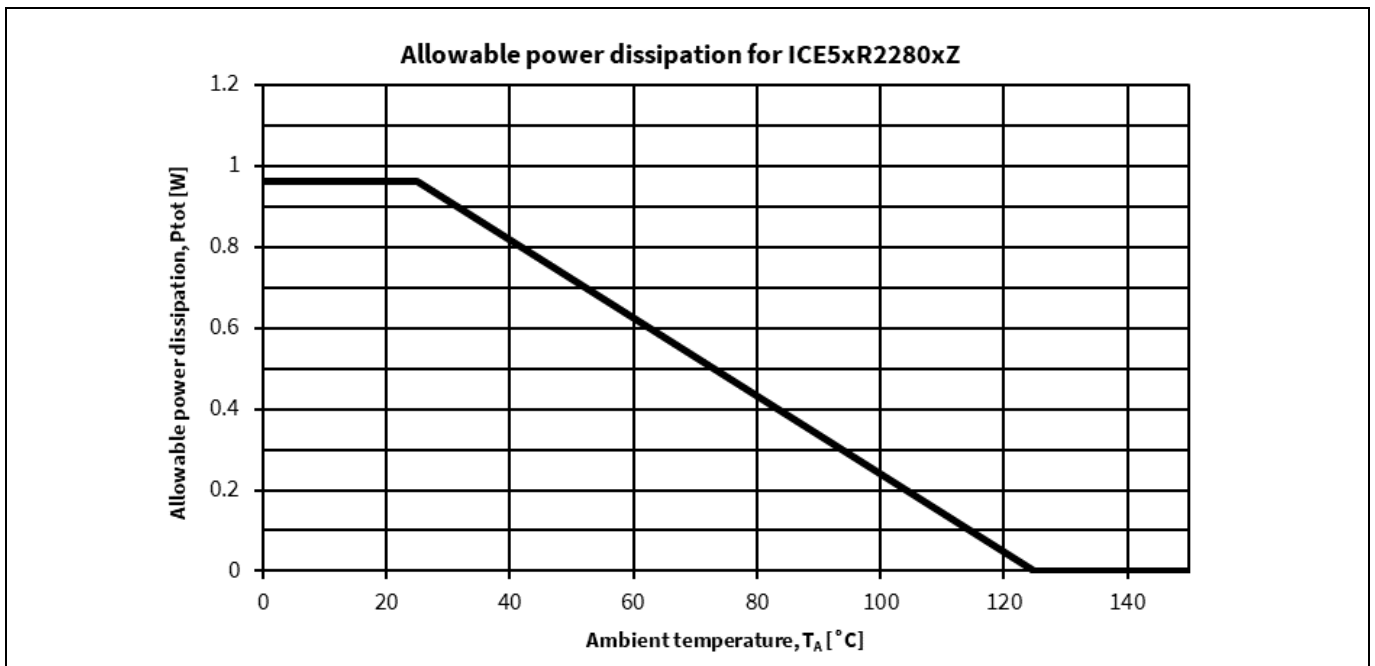


Figure 23 Power dissipation of ICE5xR2280xZ;  $P_{tot} = f(T_A)$  (Maximum ratings as given in chapter 4.1 must not be exceeded)

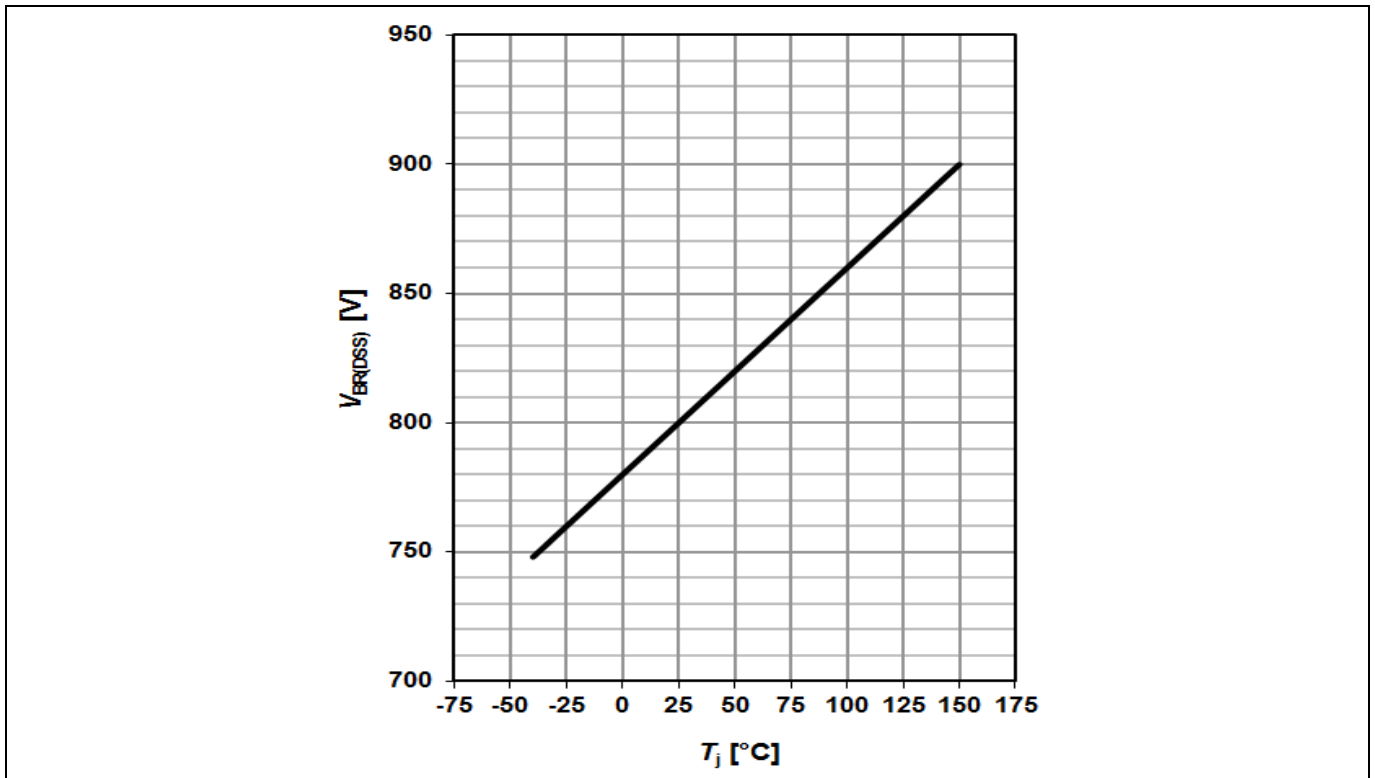


Figure 24 Drain-source breakdown voltage ICE5xRxx80xZ;  $V_{BR(DSS)} = f(T_j)$ ,  $I_D = 1$  mA

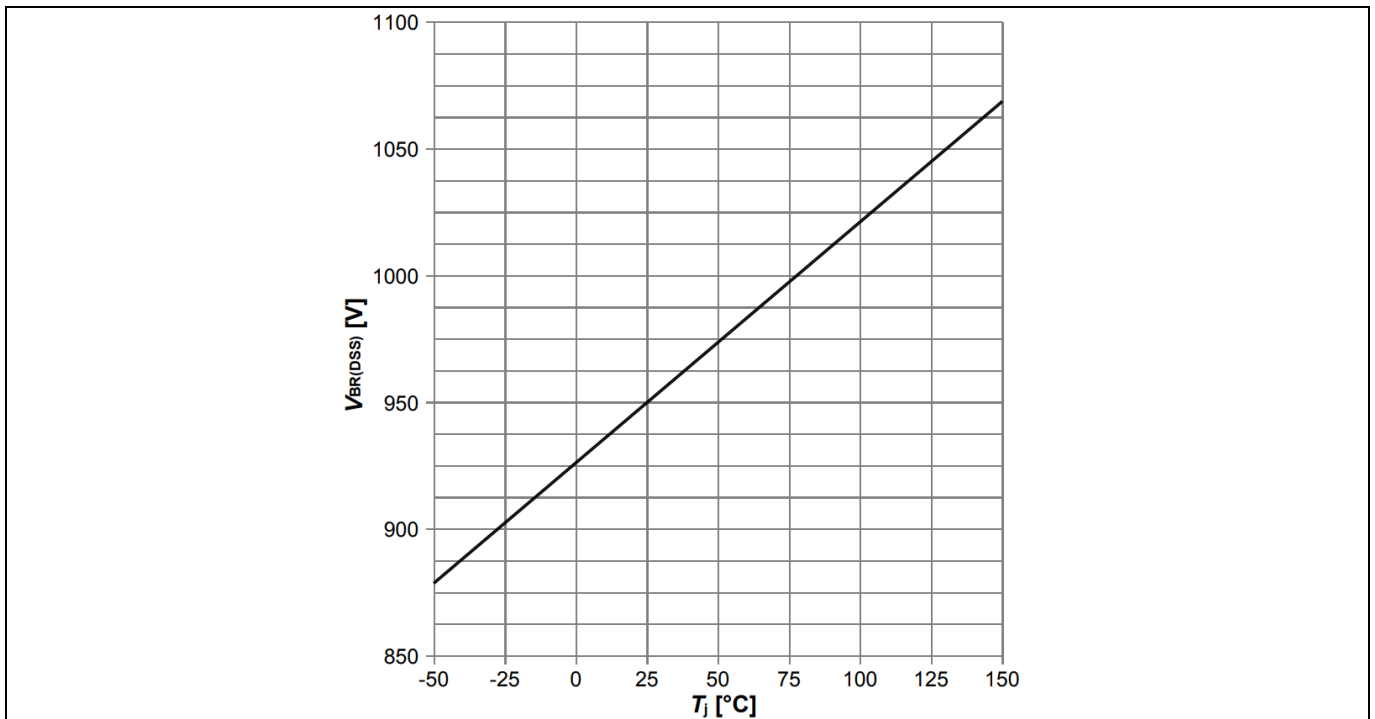


Figure 25 Drain-source breakdown voltage ICE5xR3995xZ;  $V_{BR(DSS)} = f(T_j)$ ,  $I_D = 1$  mA

CoolMOS™ performance characteristics

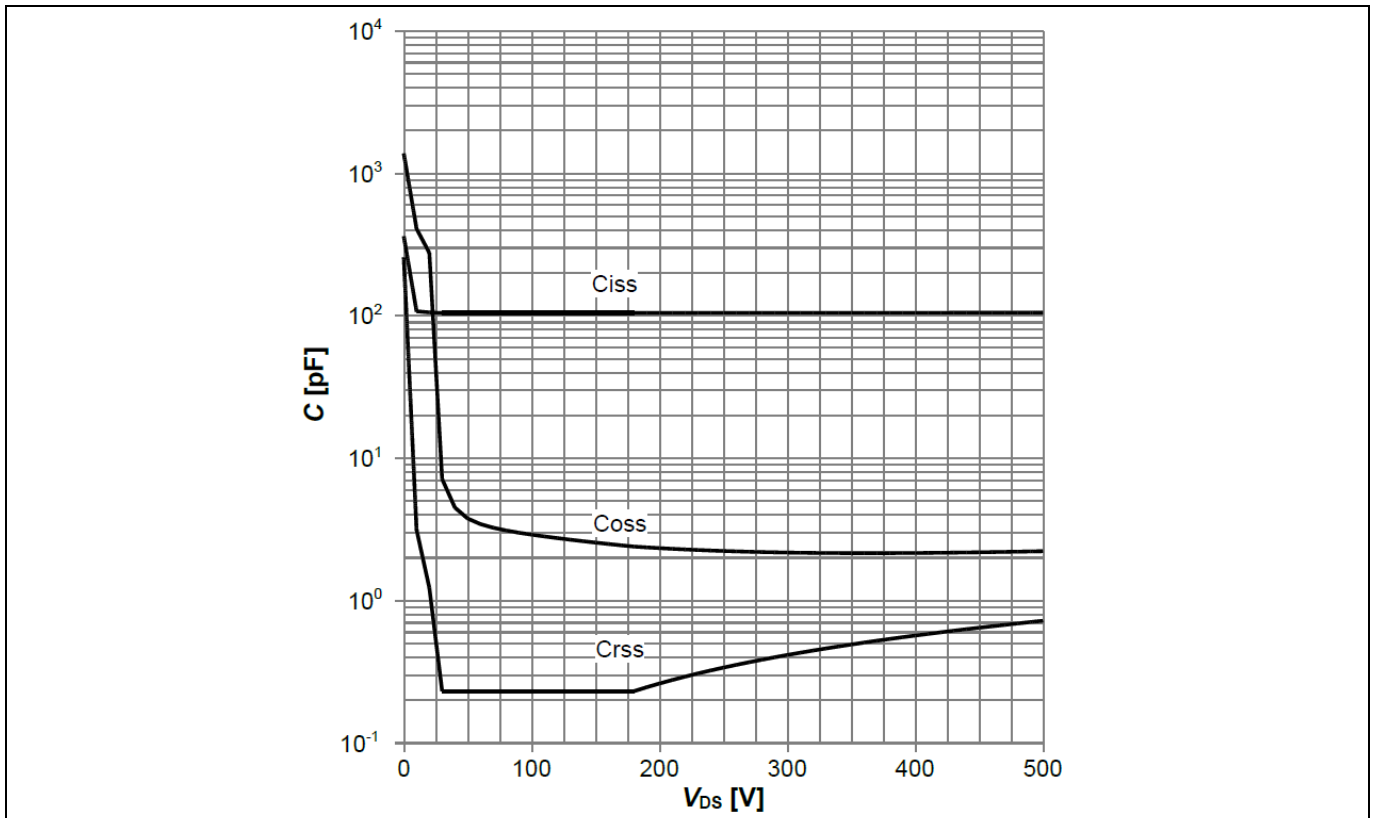


Figure 26 Typical CoolMOS™ capacitances of ICE5BR4780BZ ( $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$ )

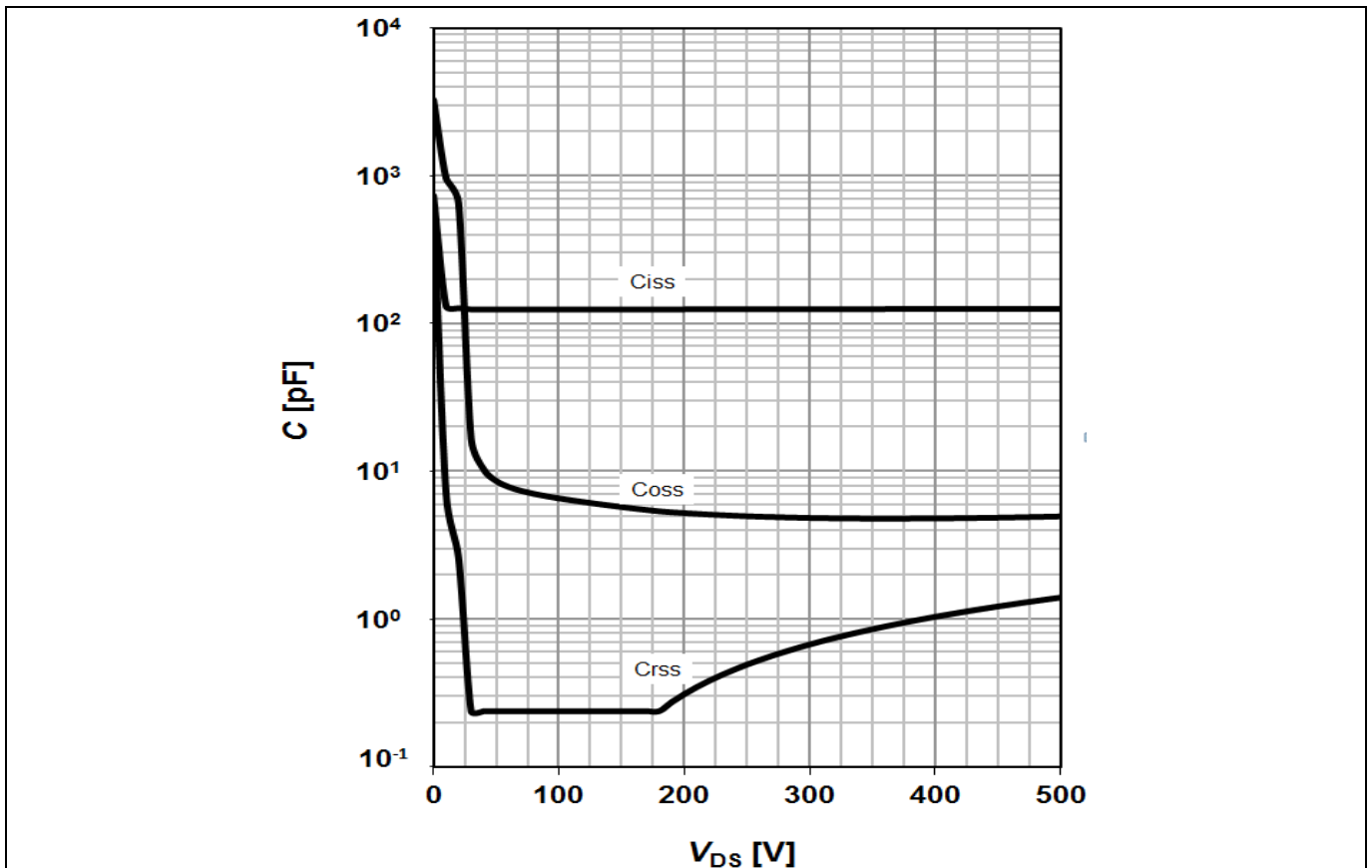


Figure 27 Typical CoolMOS™ capacitances of ICE5xR2280xZ ( $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$ )

CoolMOS™ performance characteristics

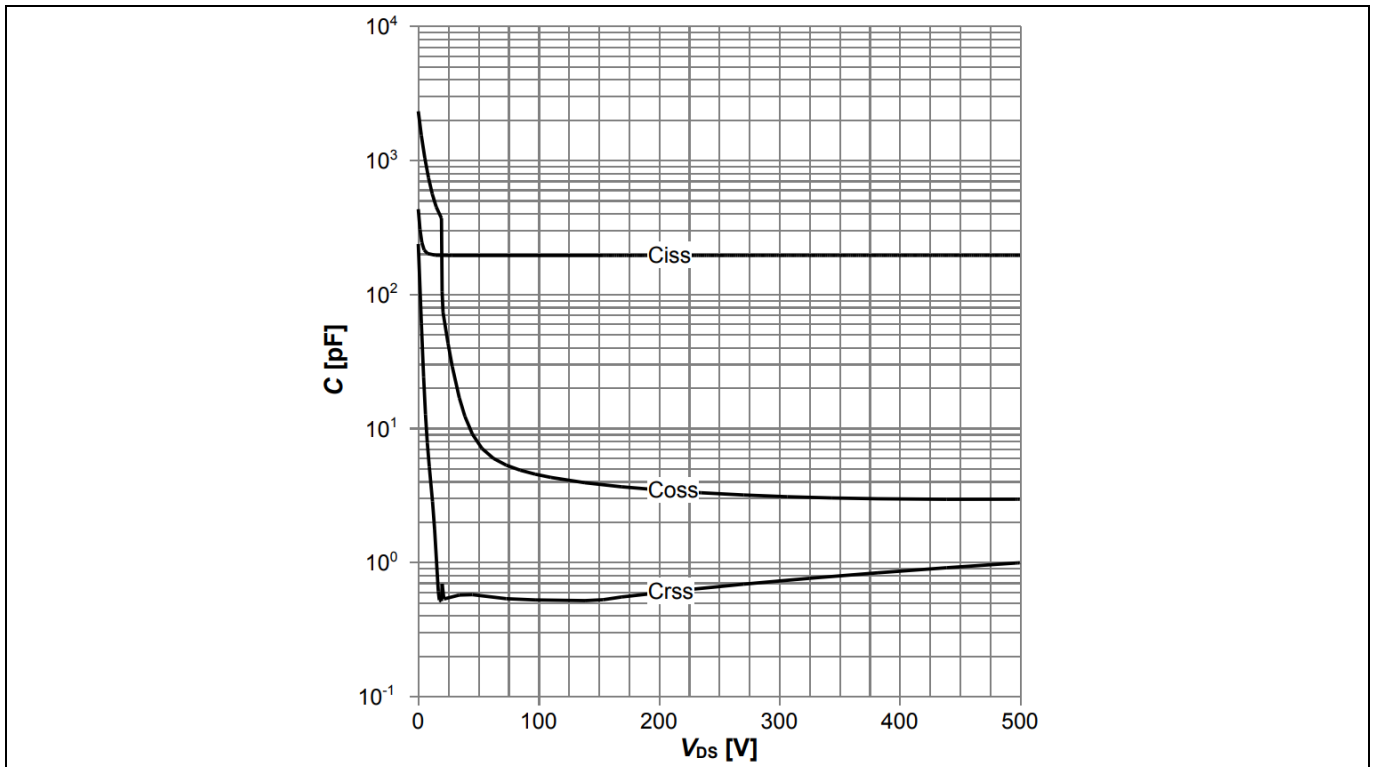


Figure 28 Typical CoolMOS™ capacitances of ICE5xR3995xZ ( $C = f(V_{DS})$ ;  $V_{GS} = 0$  V;  $f = 250$  kHz)



## 6 Output power curve

The calculated output power curves versus ambient temperature are shown below. The curves are derived based on a typical DCM/CCM flyback in an open frame design setting the maximum  $T_j$  of the integrated CoolMOS™ at 125°C, using minimum drain pin copper area in a 2 oz copper single-sided PCB and steady state operation only (no design margins for abnormal operation modes are included).

The output power figure is for selection purpose only. The actual power can vary depending on a particular design. In a power supply system, appropriate thermal design margins must be considered to make sure that the operation of the device is within the maximum ratings given in chapter 4.1.

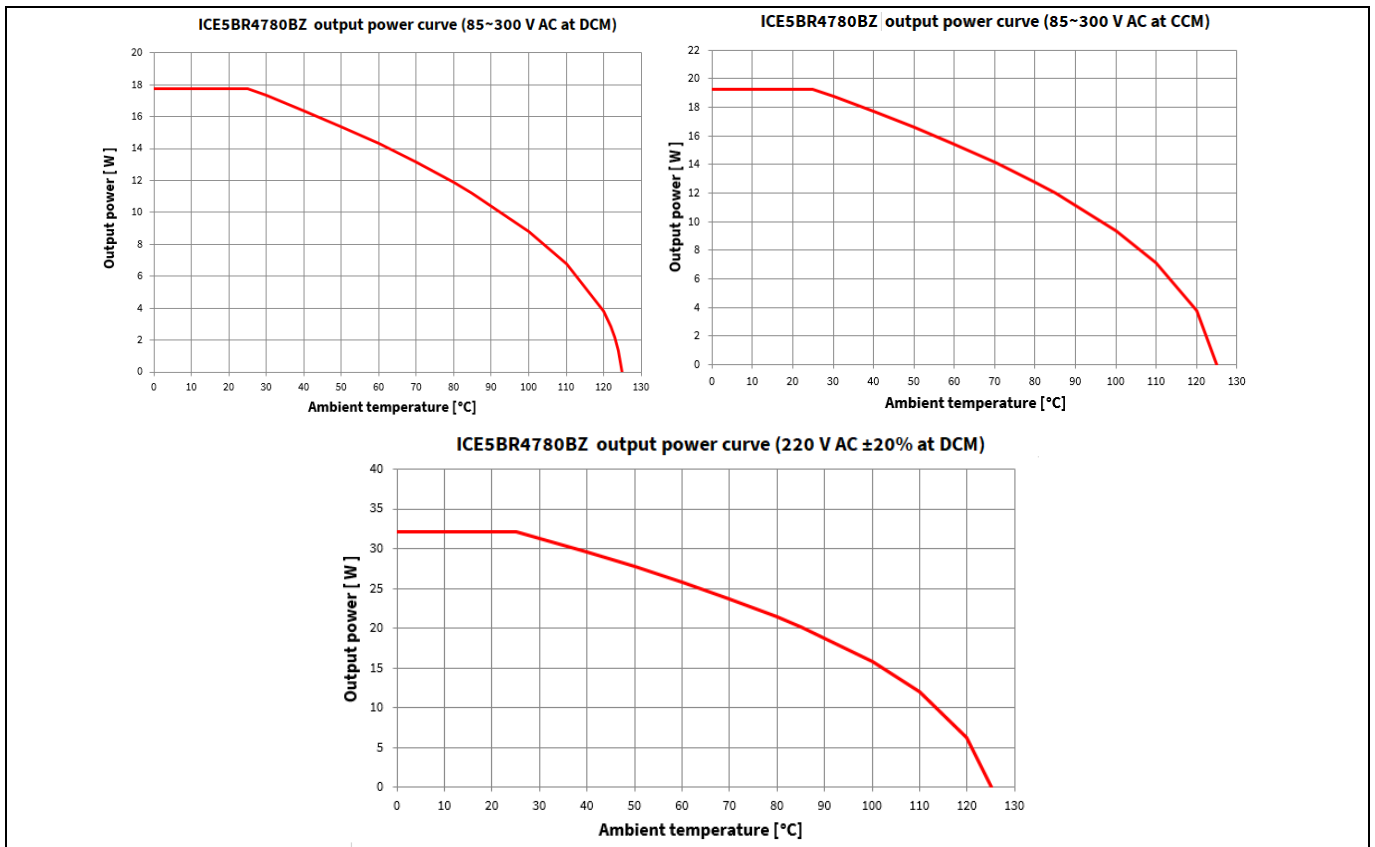


Figure 29 Output power curve of ICE5BR4780BZ

Output power curve

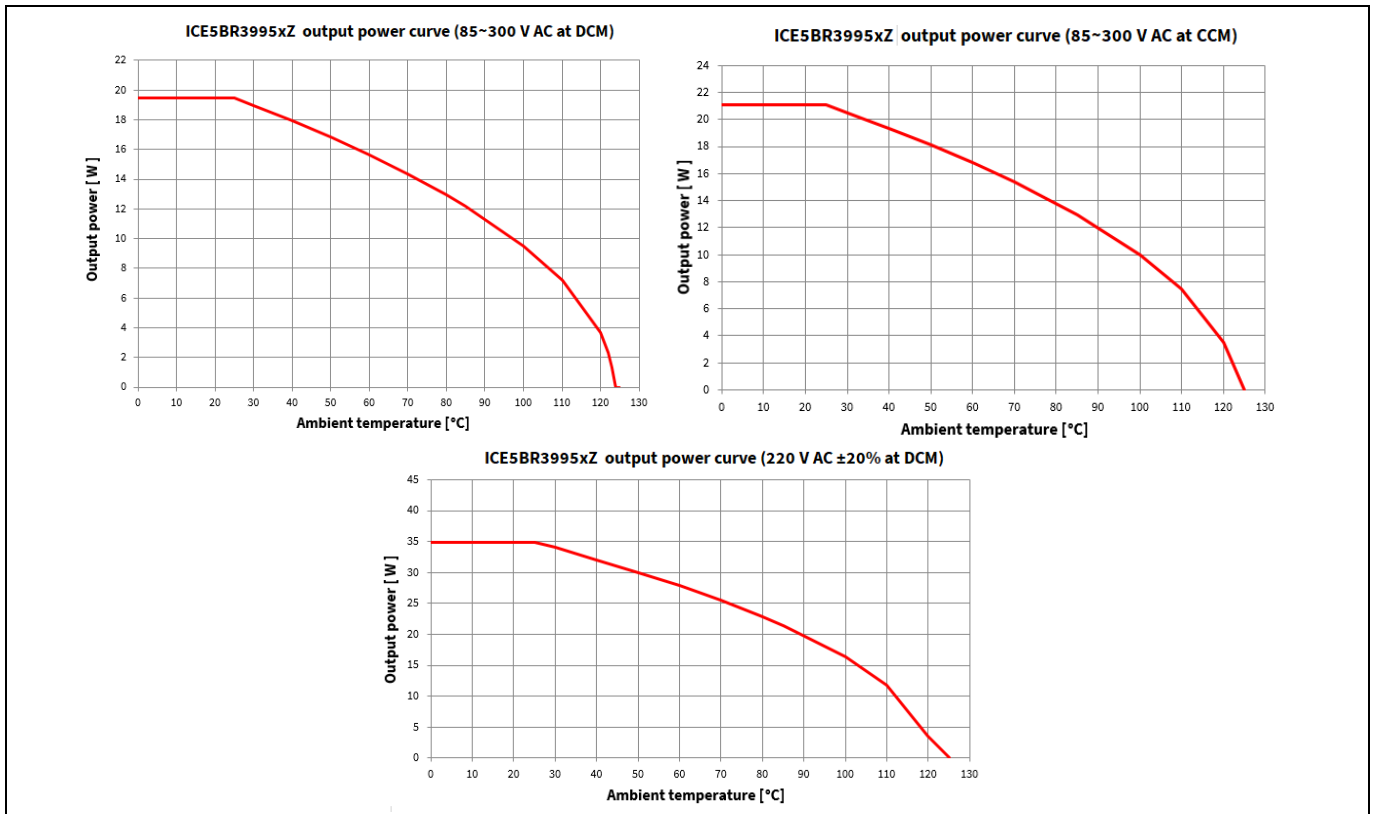


Figure 30 Output power curve of ICE5BR3995xZ

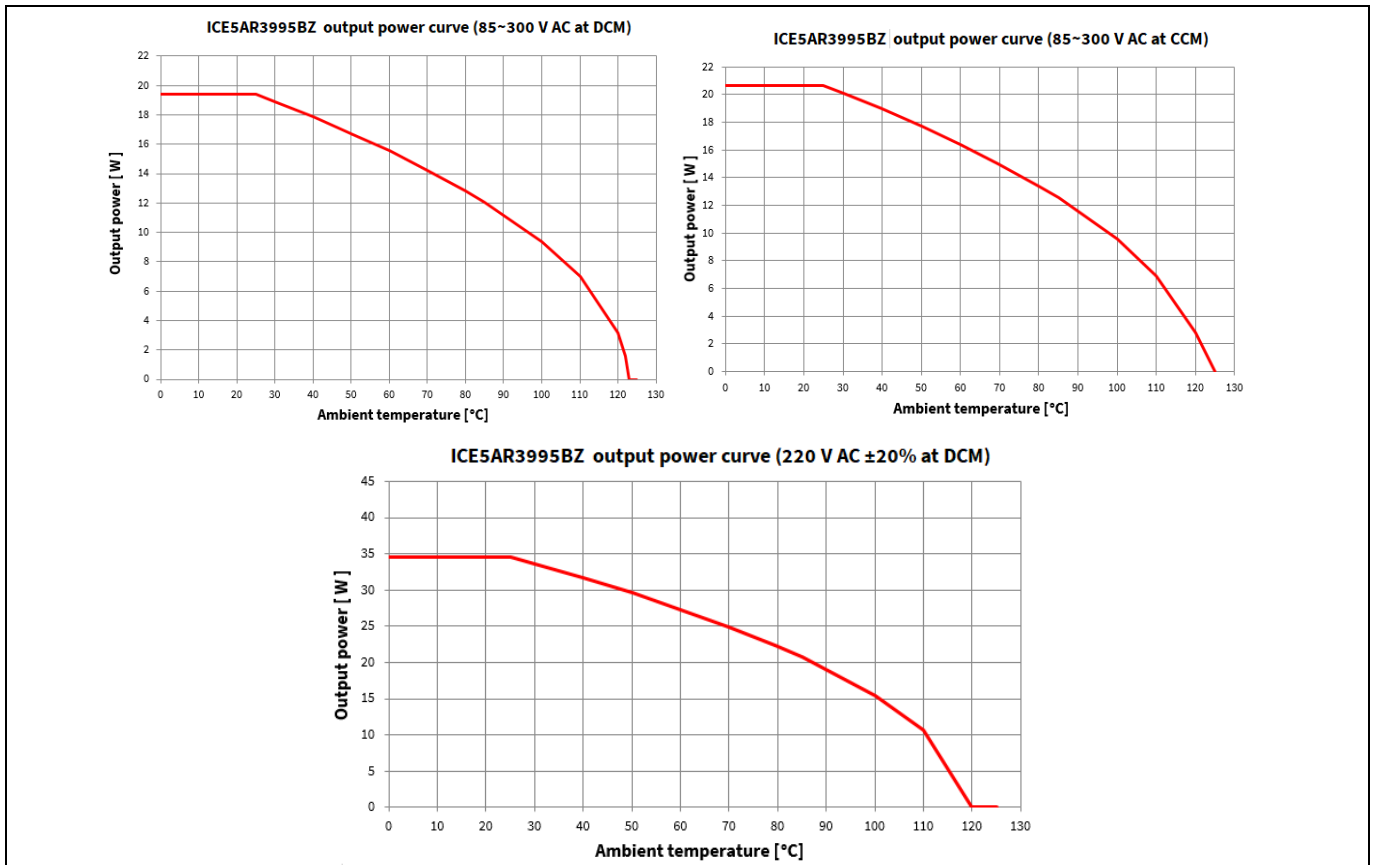


Figure 31 Output power curve of ICE5AR3995BZ

Output power curve

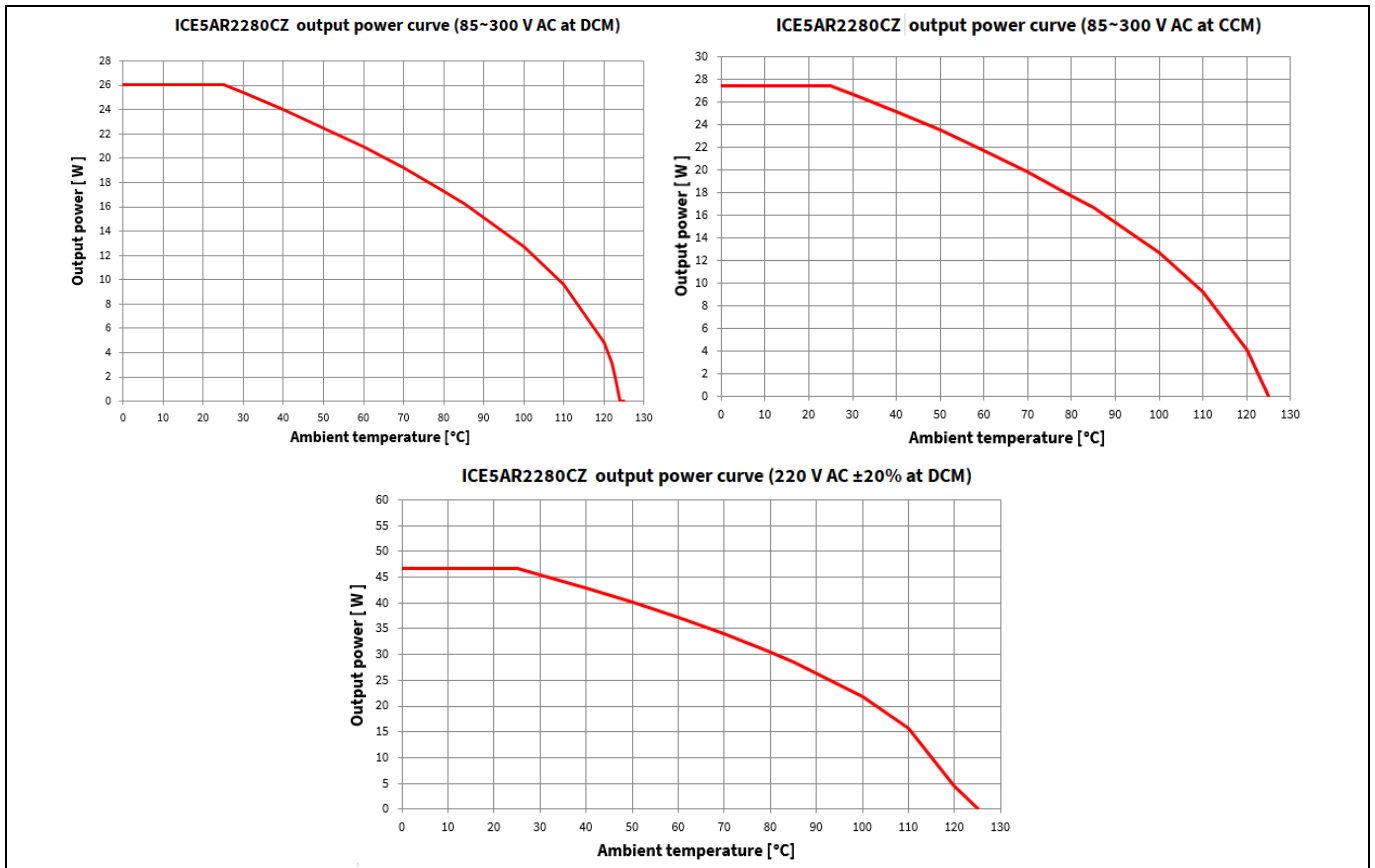


Figure 32 Output power curve of ICE5AR2280CZ

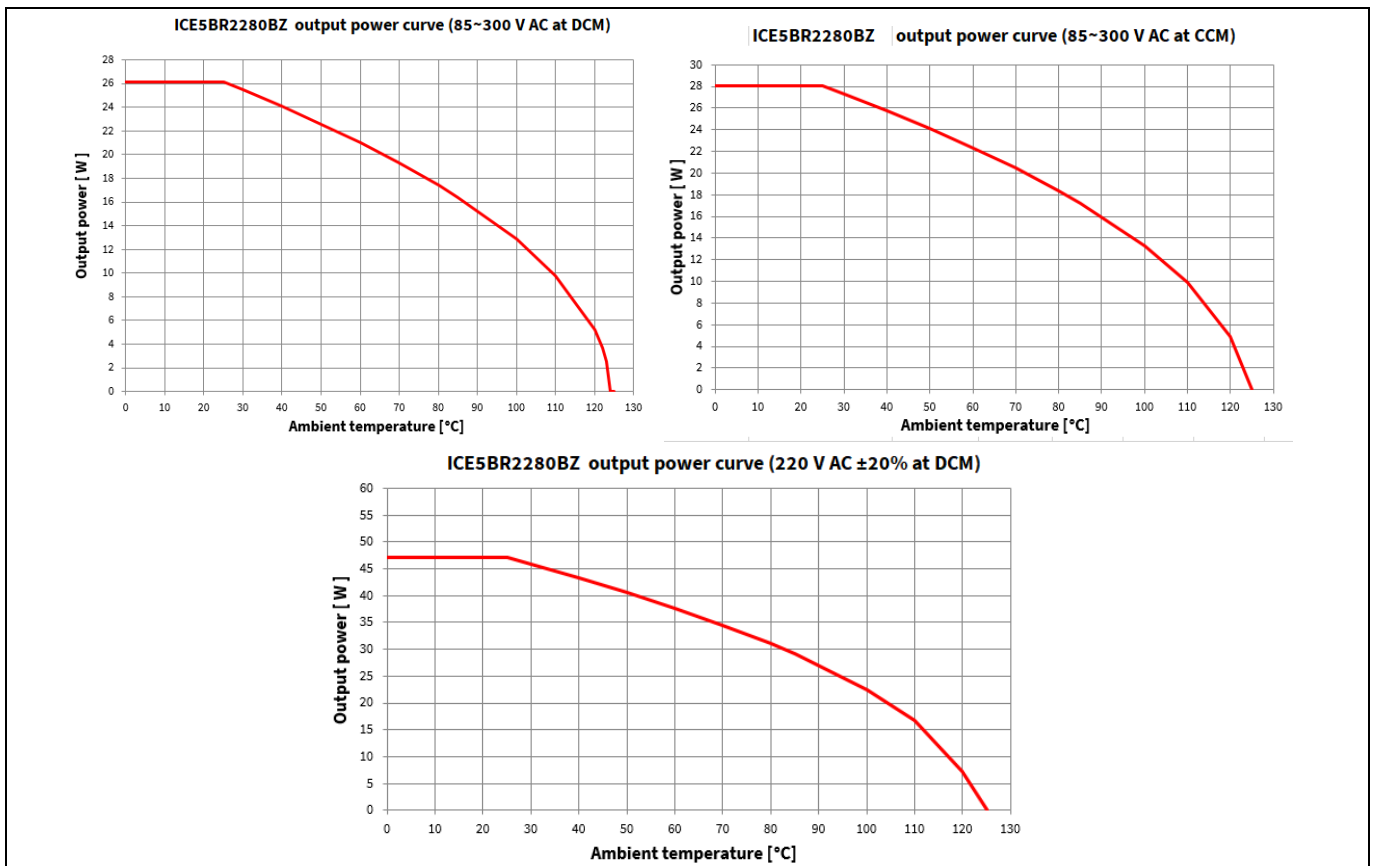
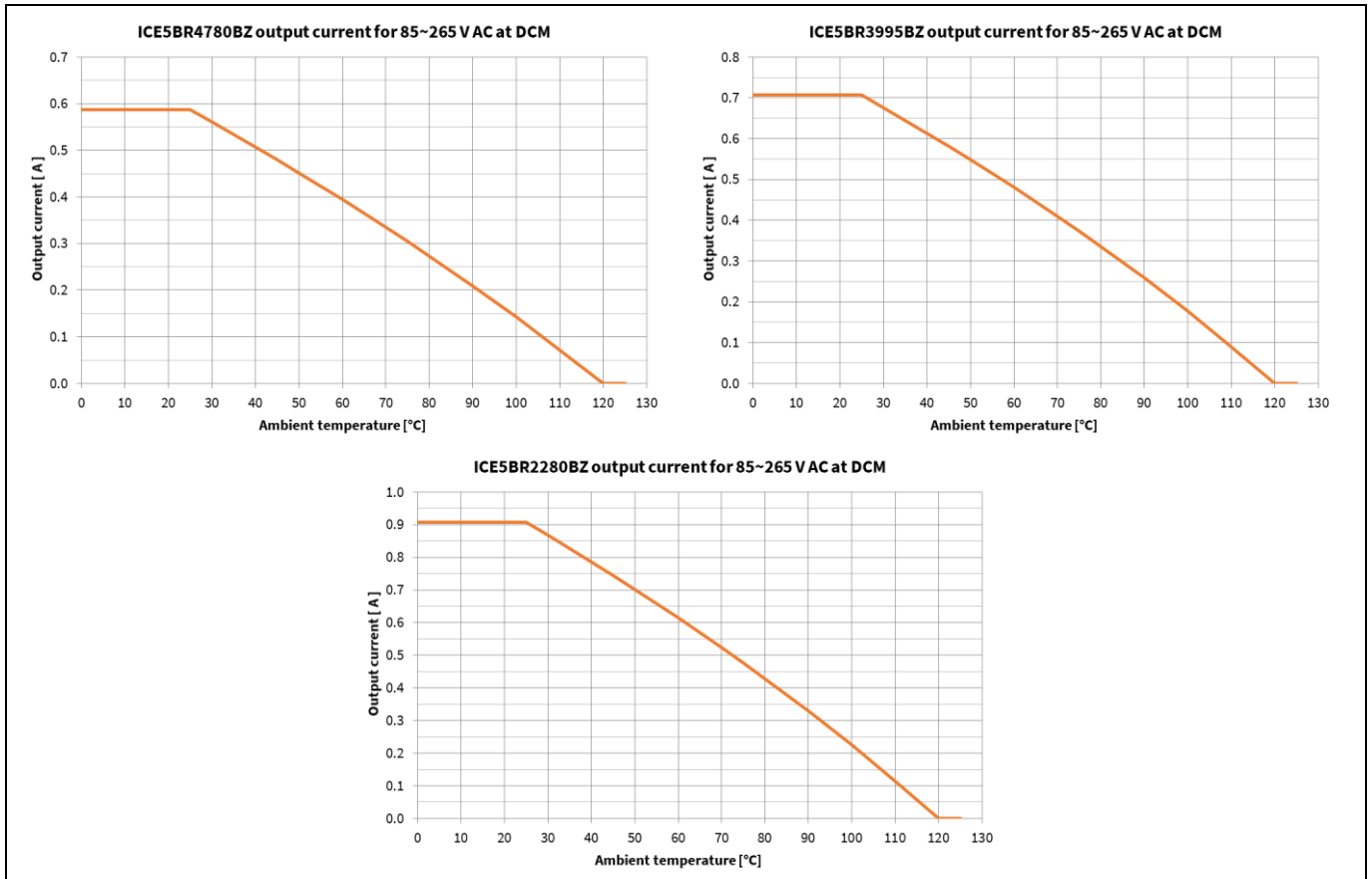


Figure 33 Output power curve of ICE5BR2280BZ

## 7 Output current curve

The calculated output current curves showing typical output power against ambient temperature are shown below. The curves are derived based on an open-frame design at  $T_a = 50^\circ\text{C}$ ,  $T_j = 125^\circ\text{C}$  (integrated HV MOSFET for CoolSET™), using the minimum 100 mm<sup>2</sup> drain pin copper area in a 2 oz copper single-sided PCB and steady-state operation only (no design margins for abnormal operation modes are included). The output power figure is for selection purposes only. The actual power can vary depending on the specific design.



**Figure 34 Output current curve of ICE5BRxxxxBZ**

## 8 Package information

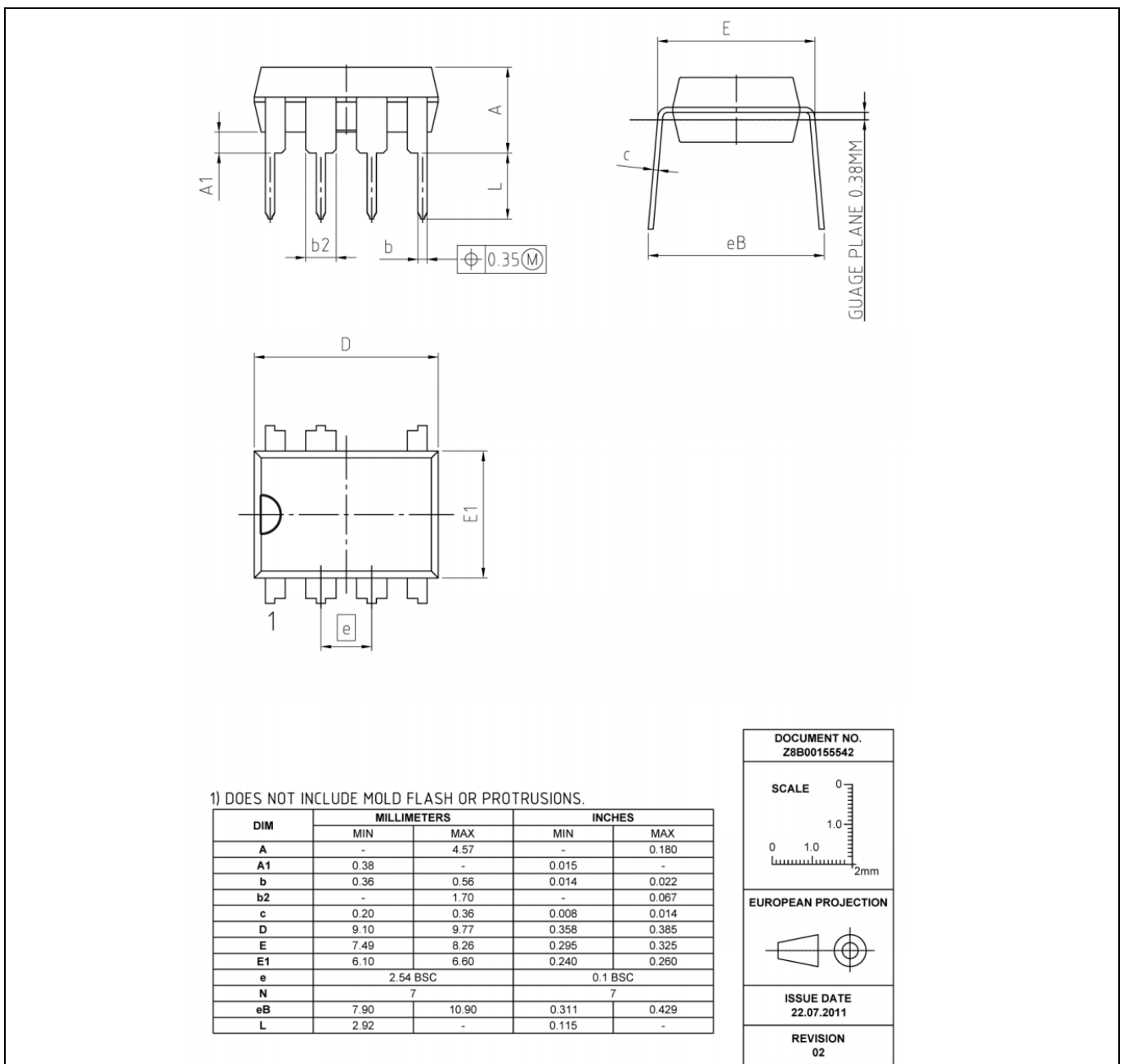


Figure 35 PG-DIP-7

### Green product (RoHS-compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations, the device is available as a green product. Green products are RoHS-compliant (i.e., Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

### Further information on packages

<https://www.infineon.com/packages>

### 8.1 Marking

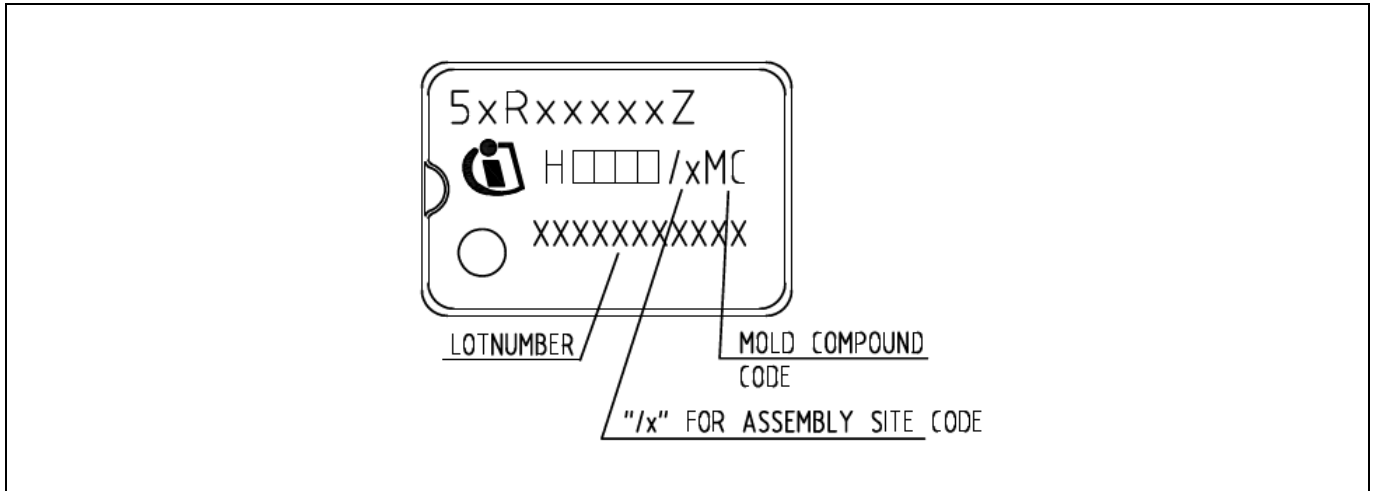


Figure 36 Marking of PG-DIP-7

## **9 Revision history**

<b>Revision</b>	<b>Date</b>	<b>Changes</b>
Rev 1.0	22 February 2022	Initial release
Rev 1.1	19 July 2022	Add new part number - ICE5AR3995BZ

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**Document reference**

**ICE5xRxxxxxZ**

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